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Kojima et al.

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(54) **ULTRASONIC TRANSDUCER, ULTRASONIC PROBE, ULTRASONIC APPARATUS, ULTRASONIC TRANSDUCER MANUFACTURING METHOD, AND VIBRATION DEVICE**

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G01N 29/24 (2006.01)

(52) **U.S. Cl.**
CPC **G01N 29/24** (2013.01); **A61B 8/00** (2013.01); **G01N 29/2437** (2013.01); **G01N 2291/101** (2013.01); **H04R 2400/00** (2013.01); **H04R 2410/00** (2013.01); **H04R 2499/11** (2013.01)

(58) **Field of Classification Search**
CPC G01N 29/24; G01N 29/2437; G01N 2291/101; A61B 8/00; H04R 2499/11; H04R 2410/00; H04R 2400/00
See application file for complete search history.

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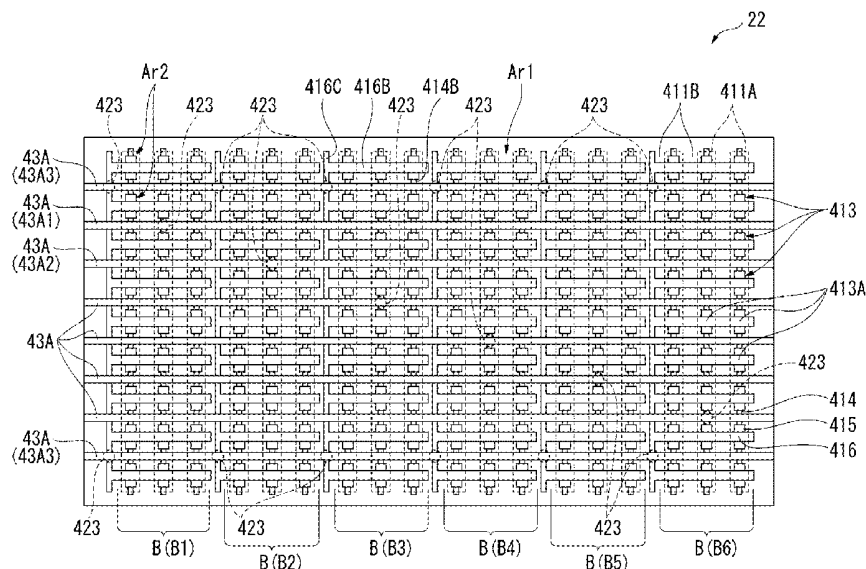
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(57) **ABSTRACT**

An ultrasonic sensor includes: a substrate in which an opening is formed; a vibration film that is provided on the substrate so as to close the opening; a plurality of vibration elements that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film; a sealing plate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to both the vibration film and the sealing plate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.

8 Claims, 11 Drawing Sheets



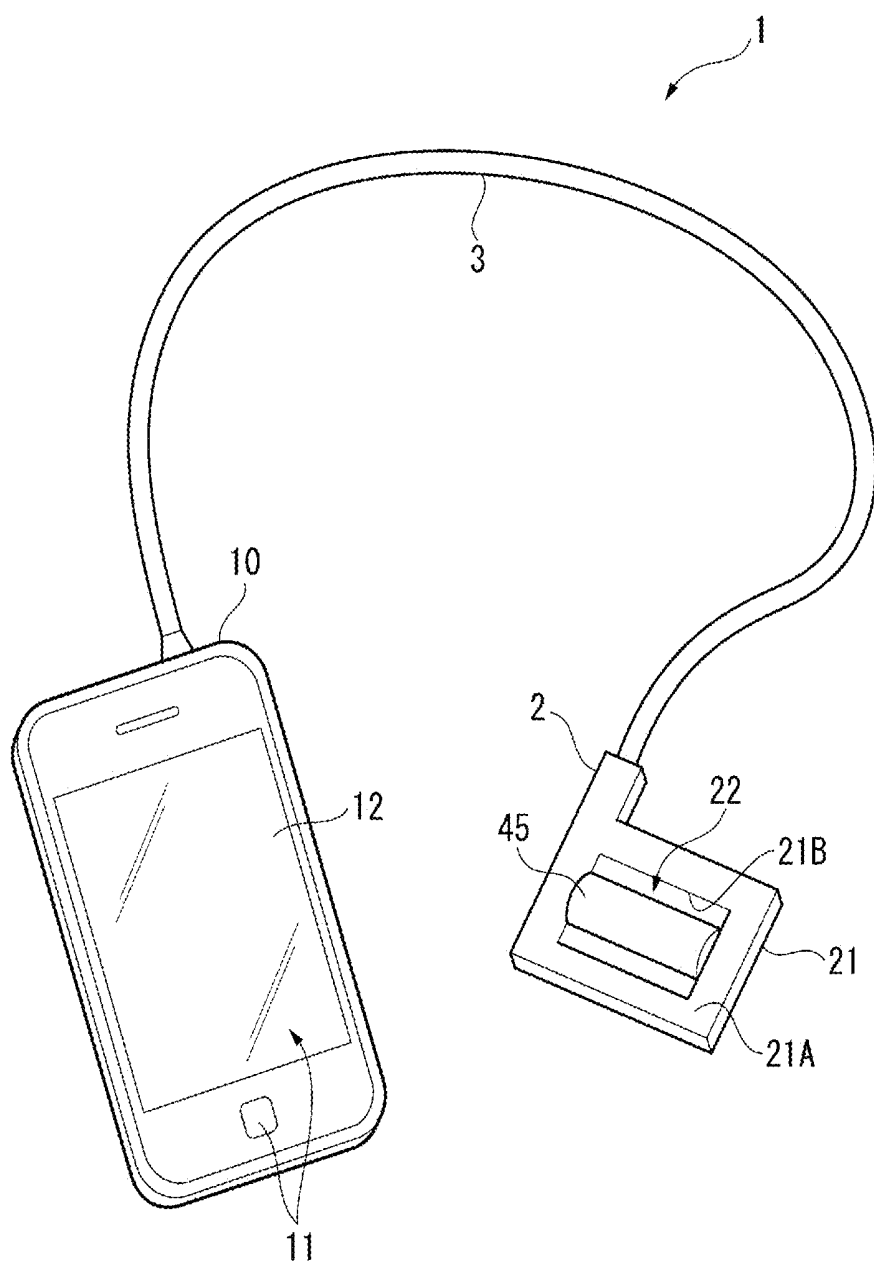


FIG. 1

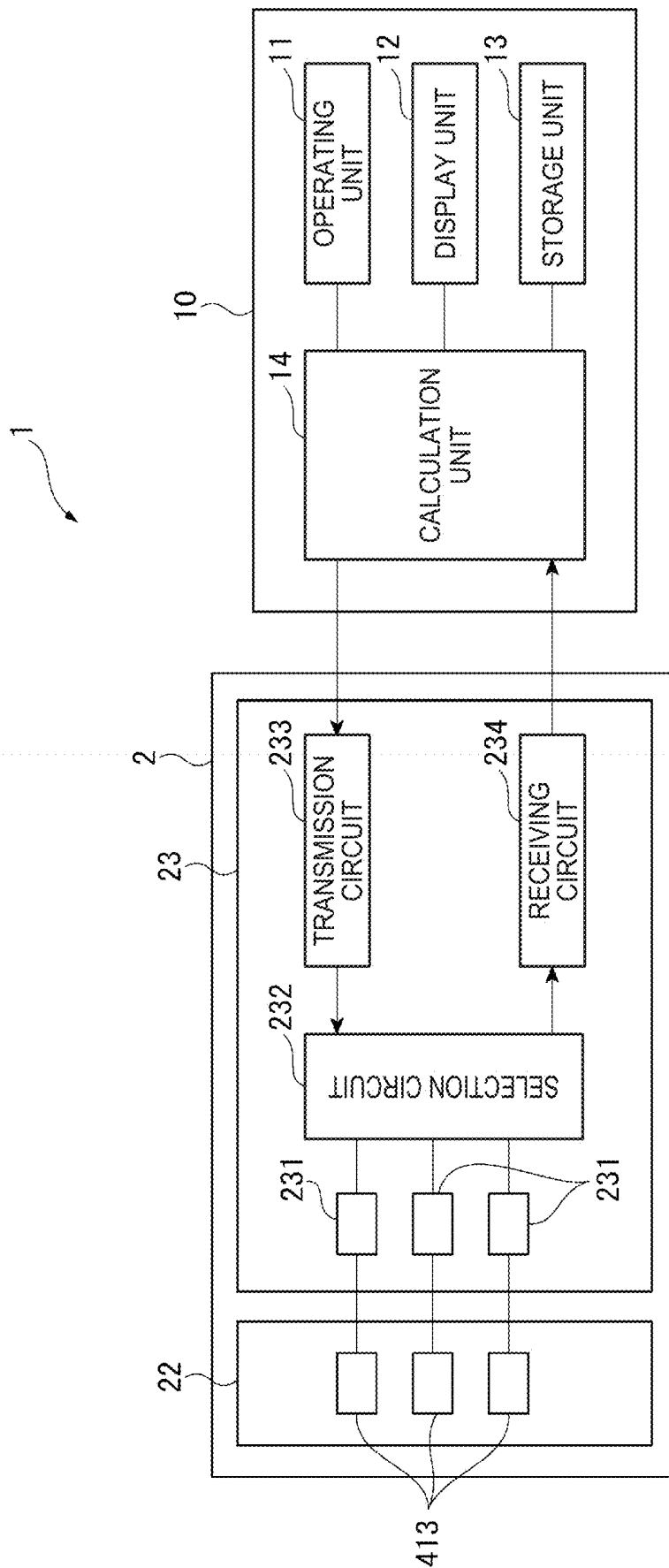


FIG. 2

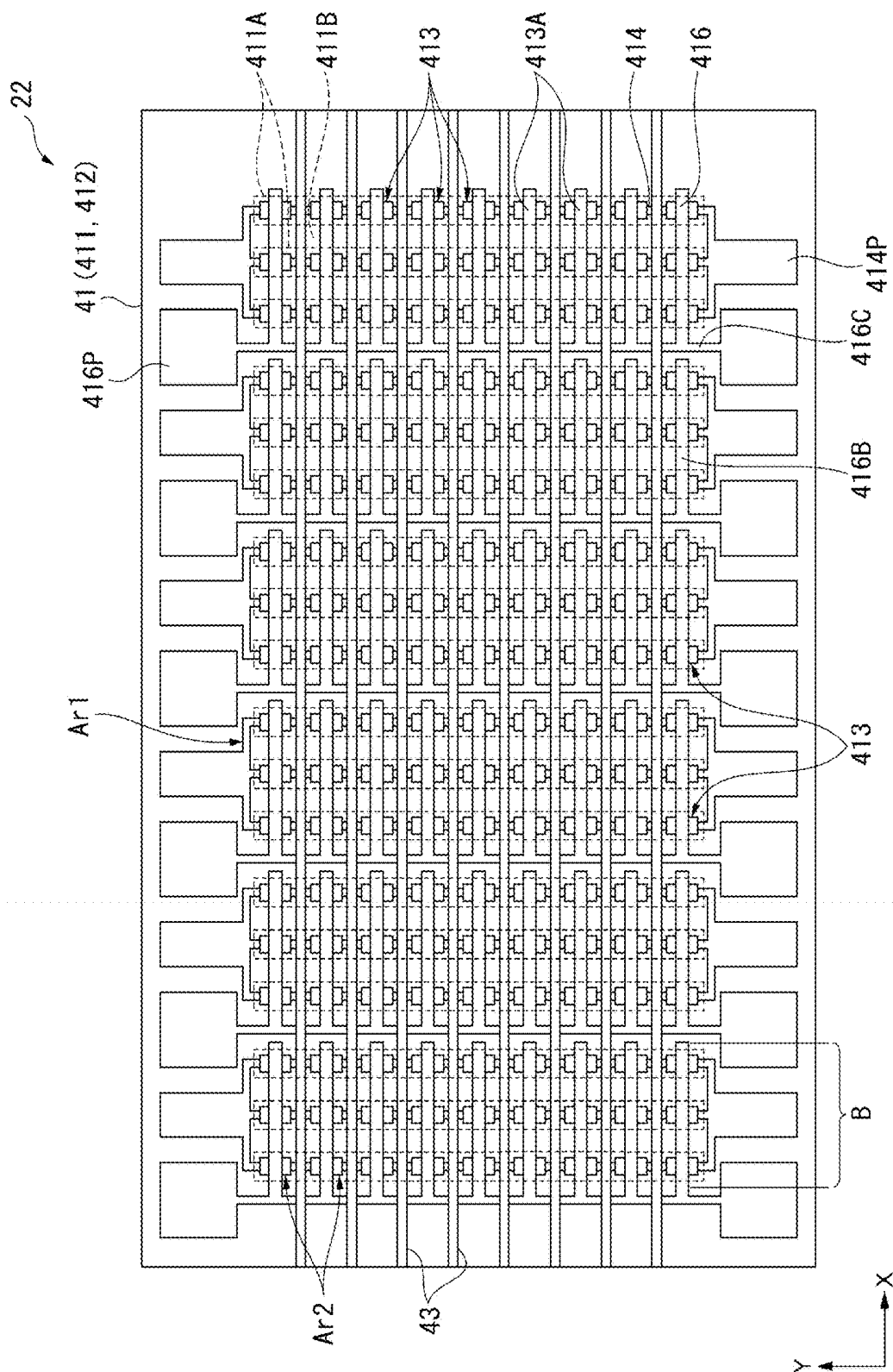


FIG. 3

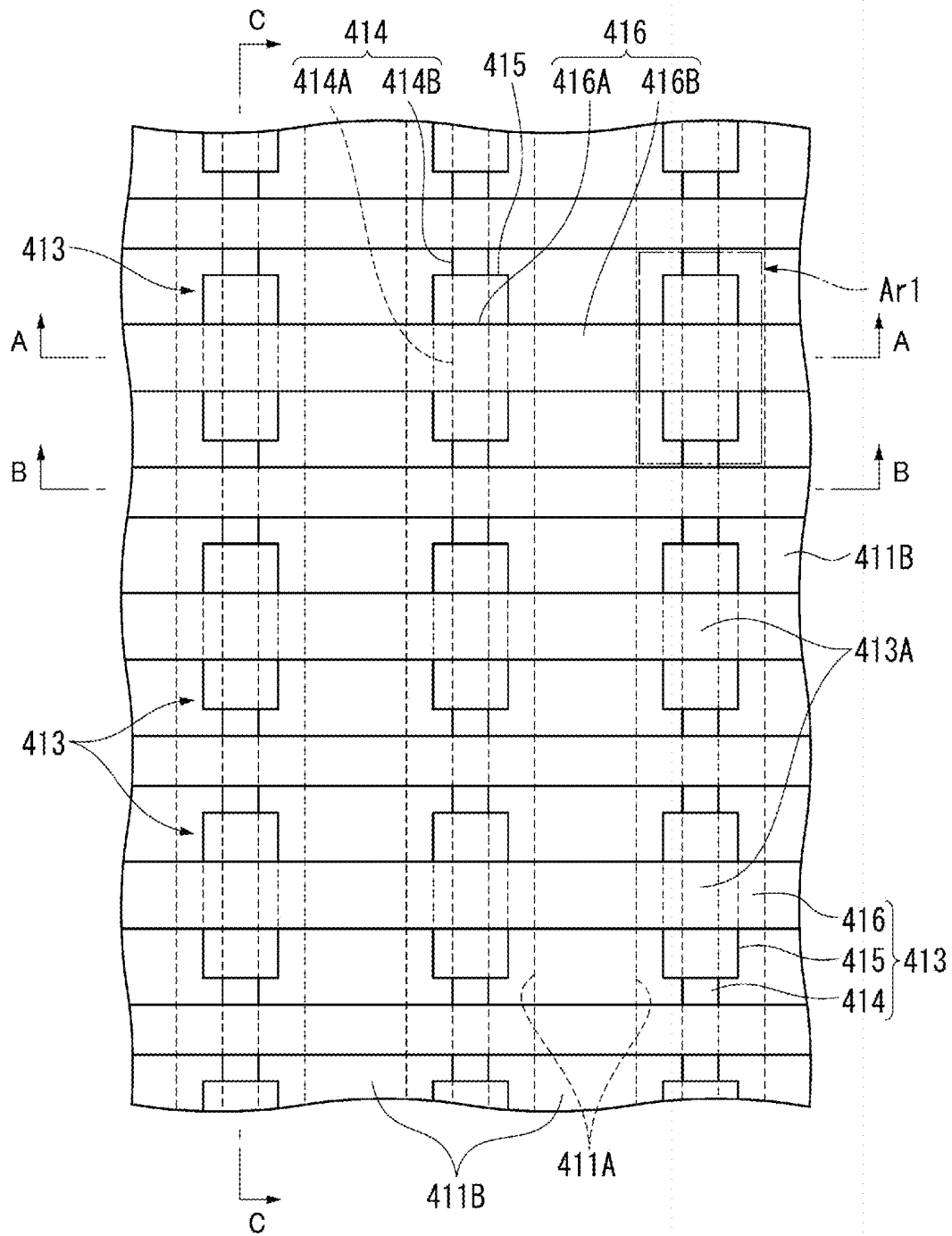


FIG. 4

FIG. 5A

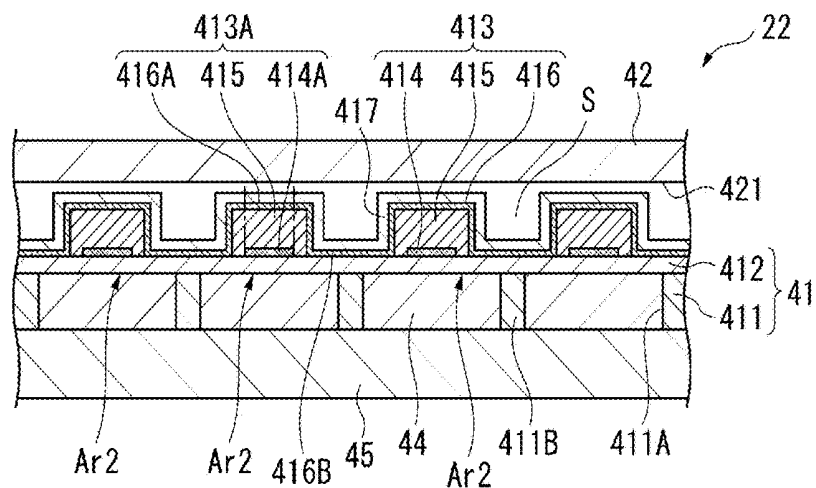


FIG. 5B

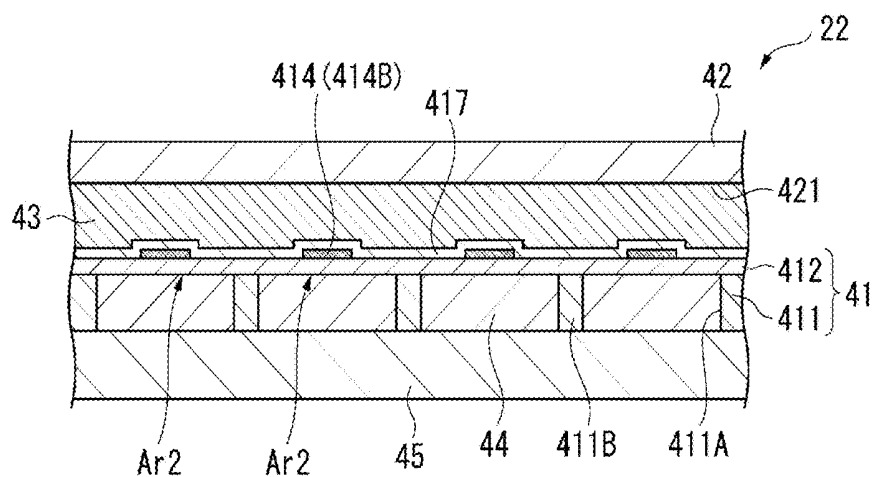


FIG. 5C

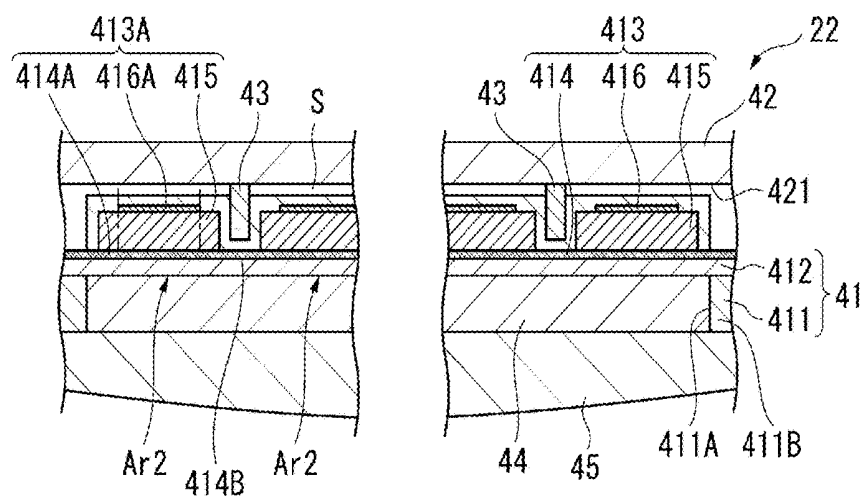


FIG. 6A

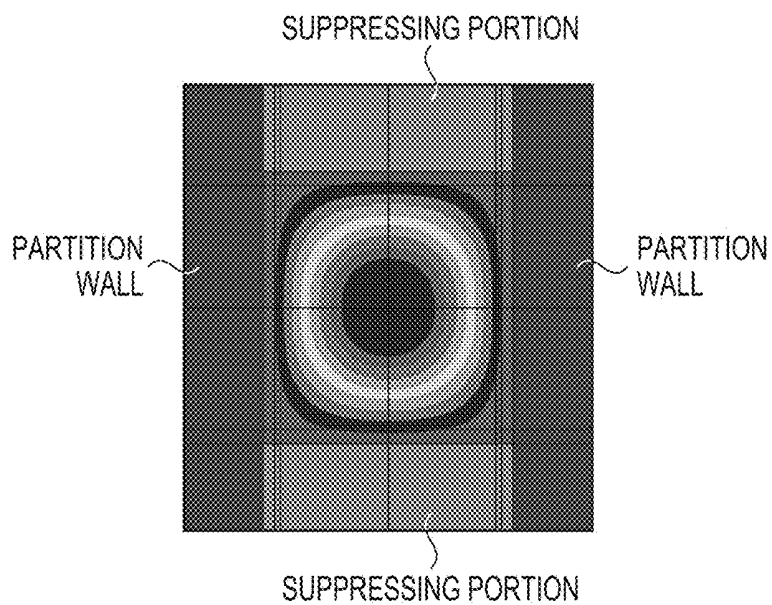


FIG. 6B

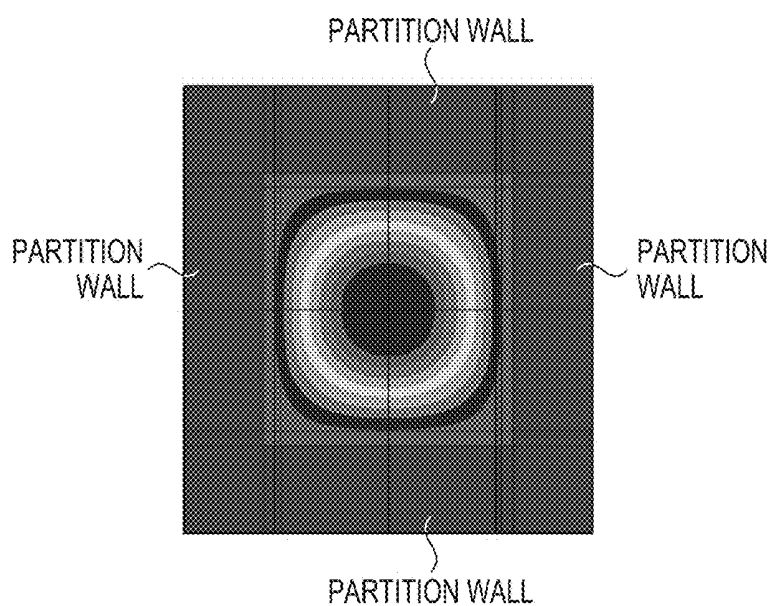
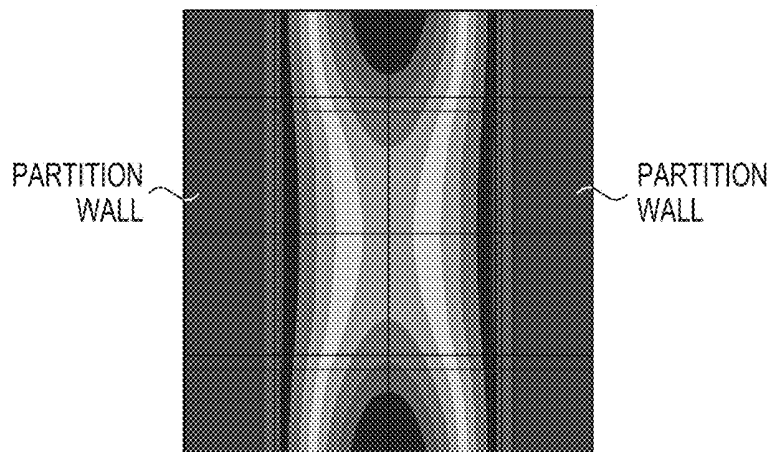


FIG. 6C



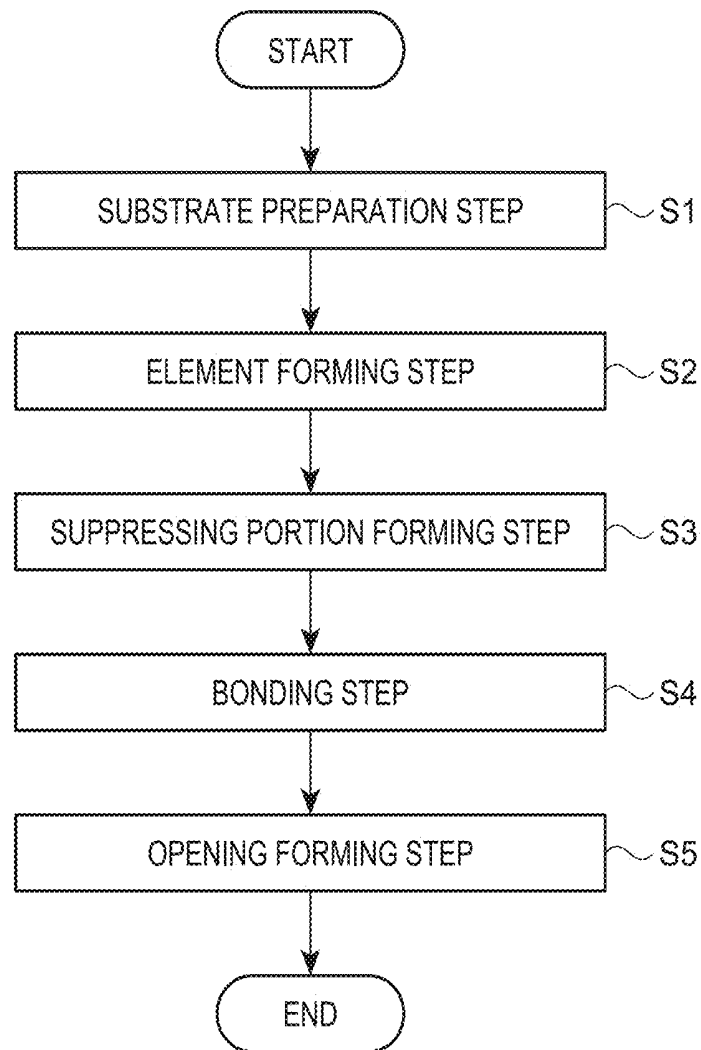


FIG. 7

FIG. 8A

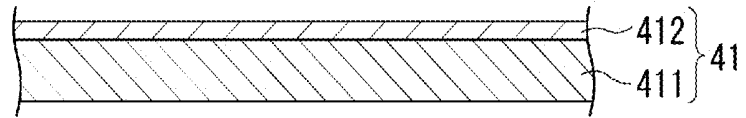


FIG. 8B

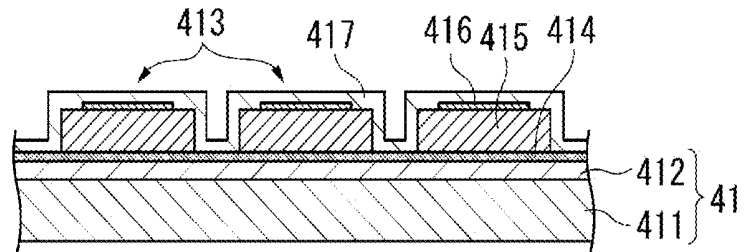


FIG. 8C

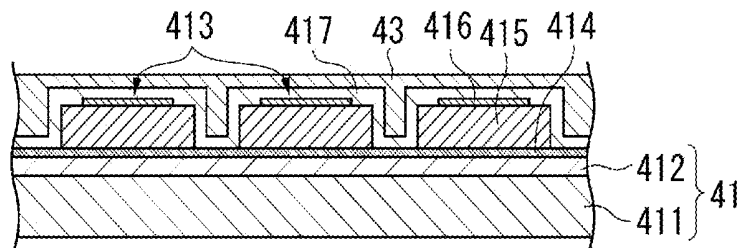


FIG. 8D

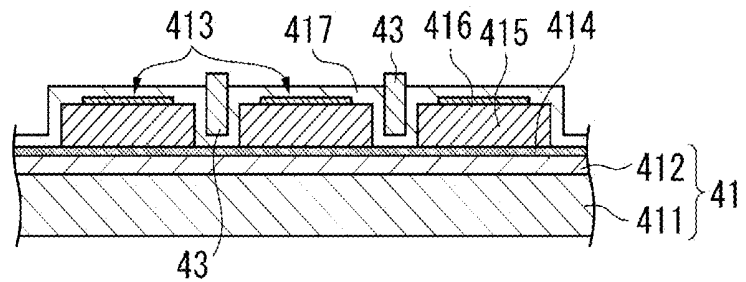


FIG. 8E

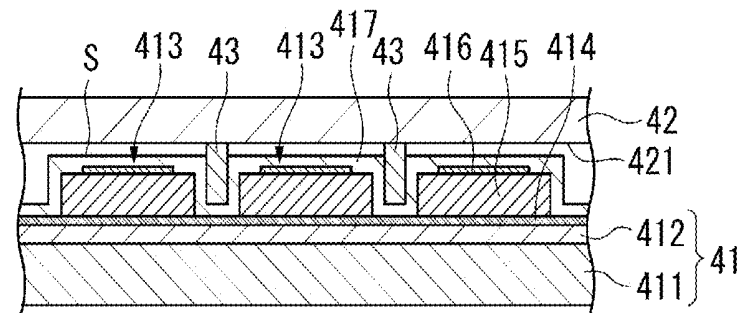
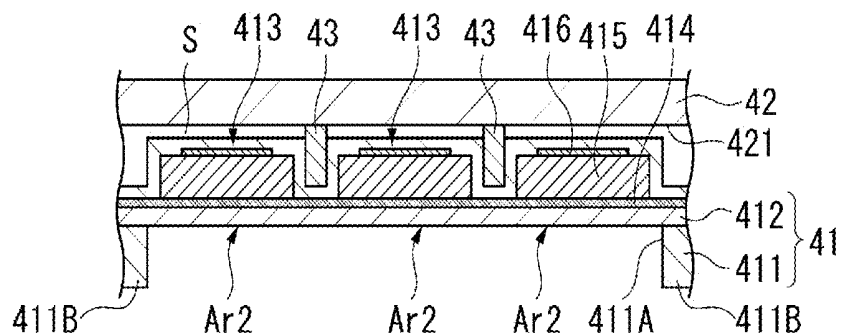


FIG. 8F



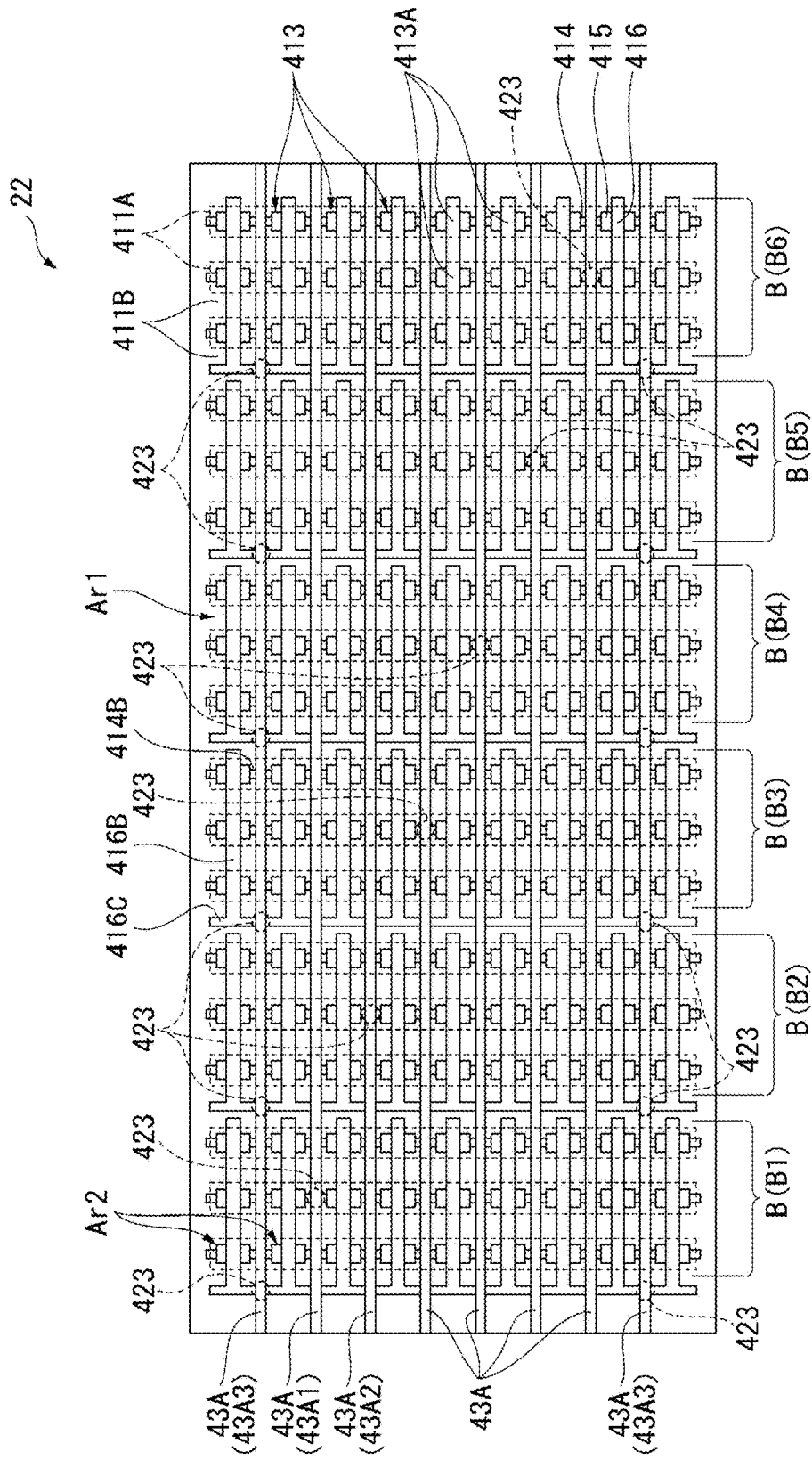


FIG. 9

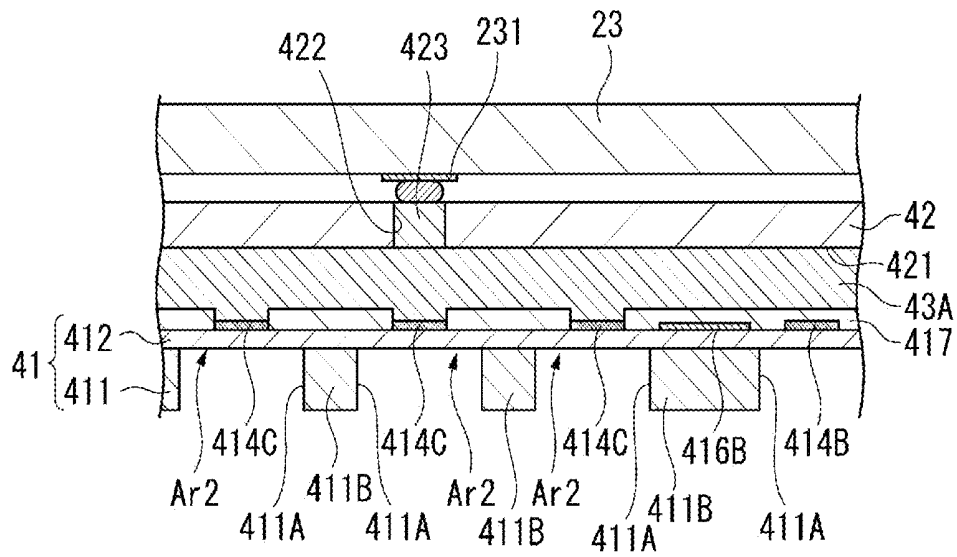


FIG. 10A

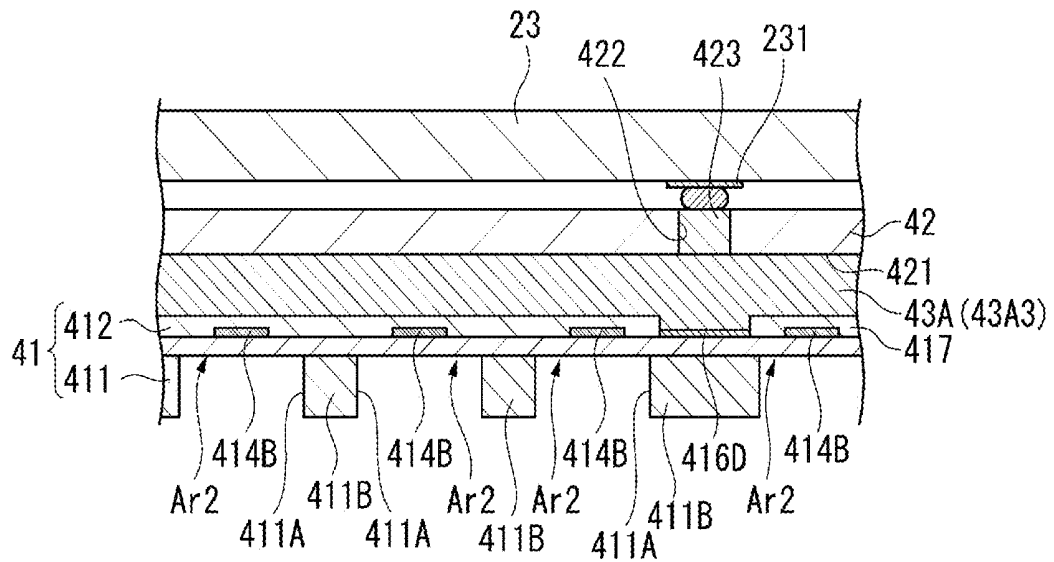


FIG. 10B

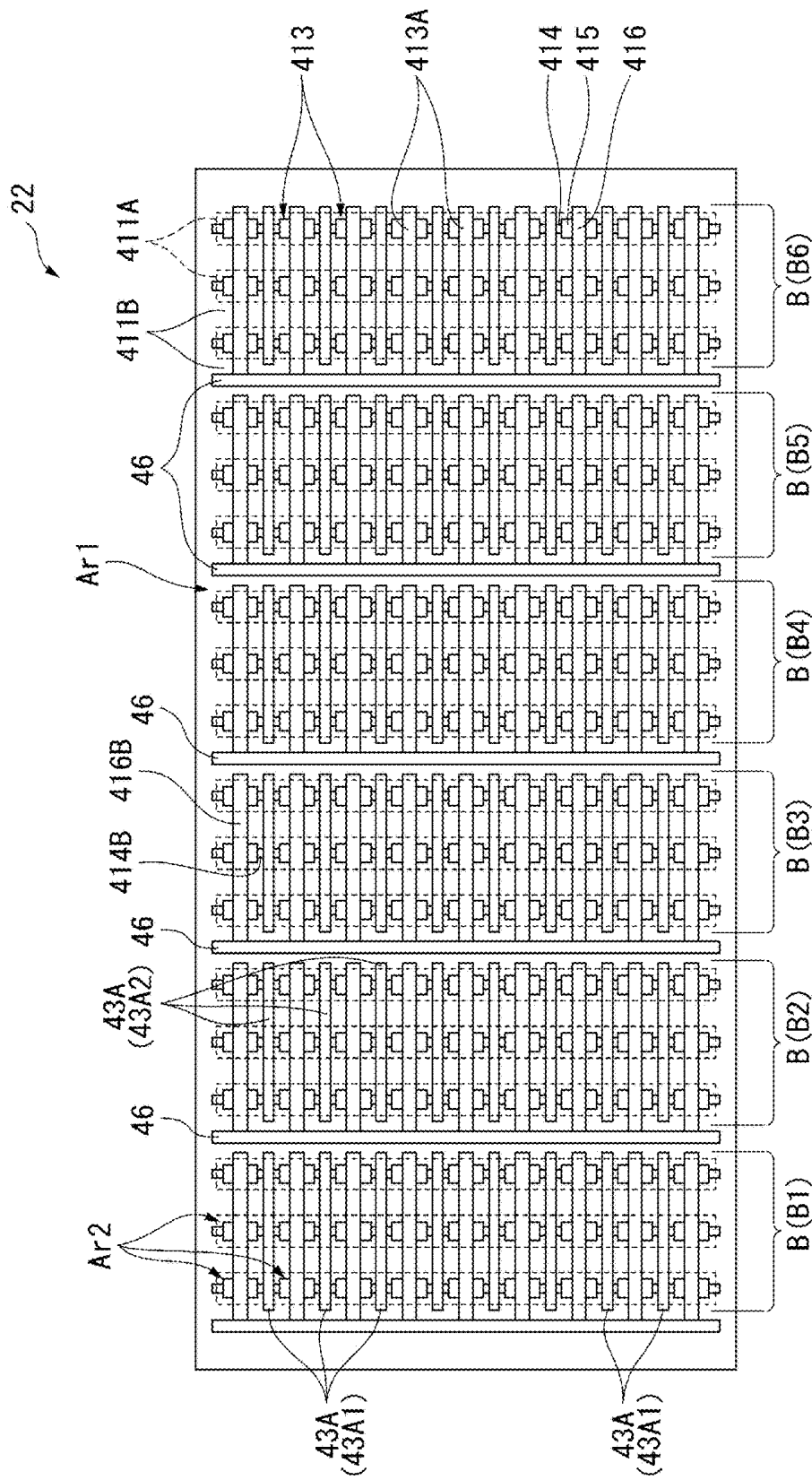


FIG. 11

**ULTRASONIC TRANSDUCER, ULTRASONIC
PROBE, ULTRASONIC APPARATUS,
ULTRASONIC TRANSDUCER
MANUFACTURING METHOD, AND
VIBRATION DEVICE**

BACKGROUND

1. Technical Field

The present invention relates to an ultrasonic transducer, an ultrasonic probe, an ultrasonic apparatus, an ultrasonic transducer manufacturing method, a vibration device, and the like.

2. Related Art

An ultrasonic transducer including a base portion having an opening and a piezoelectric element, which is provided on a vibration film that closes the opening, is known. In such an ultrasonic transducer, it is possible to transmit ultrasonic waves by driving the piezoelectric element to vibrate the vibration film or to detect (receive) the vibration of the vibration film when ultrasonic waves are input to the vibration film using the piezoelectric element (for example, refer to JP-A-2010-164331).

The efficiency of transmission or reception of ultrasonic waves in such an ultrasonic transducer depends on the distortion in the film thickness direction of a region (vibration region) of the vibration film that closes the opening. In order to improve the efficiency of transmission or reception of ultrasonic waves, it is necessary to increase the distortion of the vibration region. In this case, the two-dimensional shape of the vibration region when the ultrasonic transducer is viewed from the film thickness direction may be set to have a low aspect ratio.

Incidentally, in an ultrasonic transducer such as that disclosed in JP-A-2010-164331, the frequency of ultrasonic waves to be transmitted or received is determined by the area of the vibration region. In particular, in transmission and reception of high-frequency ultrasonic waves, it is necessary to further reduce the area of the vibration region. On the other hand, as described above, in order to efficiently transmit and receive ultrasonic wave, it is necessary to set the vibration region to have a low aspect ratio. In the configuration disclosed in JP-A-2010-164331, in a case where the area of the vibration region is set to be small and a low aspect ratio is set, it is necessary to form the opening provided in the base portion very small. Accordingly, there is a problem that manufacturing is difficult and the mass productivity is lowered.

SUMMARY

An advantage of some aspects of the invention is to provide an ultrasonic transducer having high ultrasonic wave transmission and reception efficiency and excellent in mass productivity, an ultrasonic probe, an ultrasonic apparatus, an ultrasonic transducer manufacturing method, and a vibration device.

An ultrasonic transducer according to this application example includes: a substrate in which an opening is formed; a vibration film that is provided on the substrate so as to close the opening; a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film; a support substrate that is disposed so as to

face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.

According to this application example, the vibration film is provided on the substrate having an opening so as to close the opening, and a plurality of vibration elements are provided in a region where the opening and the vibration film overlap each other. Between the plurality of vibration elements of the vibration film, the suppressing portion formed of a resin material for suppressing the transmission of vibration of the vibration film is provided.

In such a configuration, in a case where a position (vibration region) where the vibration element is provided in the vibration film vibrates, the transmission of the vibration to a region other than the vibration region is suppressed by the suppressing portion. That is, even in a case where the opening is large, the aspect ratio of the vibration region can be set to a low aspect ratio by the suppressing portion. Accordingly, the distortion of the vibration film in the vibration region in the film thickness direction is increased. As a result, it is possible to output high-output (large sound pressure) ultrasonic waves at the time of driving processing by the vibration element (at the time of ultrasonic wave transmission), and it is possible to improve reception sensitivity at the time of detection processing by the vibration element (at the time of ultrasonic wave reception).

In addition, since this is a configuration in which a plurality of vibration elements are provided for one opening, it is possible to increase the size of the opening compared with, for example, a configuration in which one vibration element is provided for one opening. Therefore, since it is easy to form an opening, it is possible to obtain an ultrasonic transducer excellent in mass productivity.

In addition, since the suppressing portion is formed of a resin material, the vibration film and the support substrate can be easily bonded to each other by the suppressing portion using, for example, heat bonding. Therefore, it is possible to further improve the manufacturing efficiency. The suppressing portion formed of such a resin material can be formed on the vibration film easily and highly accurately by, for example, photolithography. That is, the suppressing portion can be accurately formed at a position corresponding to the vibration region corresponding to each vibration element in the vibration film. Accordingly, it is possible to suppress the inconvenience that the vibration of the vibration region is inhibited by the suppressing portion due to, for example, the shift of the position of the suppressing portion from the vibration region, it is possible to further improve the efficiency of transmission or reception.

In the ultrasonic transducer according to the application example, it is preferable that a connection wiring line connected to the vibration element is provided on the vibration film and that the suppressing portion contains a conductive filler and is connected to the connection wiring line.

In the application example with this configuration, the connection wiring line connected to the vibration element is provided on the vibration film, and is connected to the suppressing portion containing a conductive filler. In such a configuration, at a position close to the vibration element, it is possible to input and output signals from the suppressing portion to the vibration element. That is, in the related art, the connection wiring line of the vibration element is drawn

out to the outer peripheral portion of the vibration film, and is connected to a terminal of an external circuit by, for example, a flexible printed circuit (FPC) or wire bonding. In this case, since the connection wiring line becomes long and the electric resistance increases, attenuation (voltage drop) of a signal input to and output from the vibration element occurs. In contrast, in the application example, since a signal can be input and output from the suppressing portion disposed at a position close to the vibration element as described above, it is possible to suppress a voltage drop. Therefore, it is possible to improve the driving efficiency of the ultrasonic transducer. That is, when transmitting ultrasonic waves from the ultrasonic transducer, ultrasonic waves having a desired output value can be appropriately output. In addition, in the case of receiving ultrasonic waves in the ultrasonic transducer, it is possible to acquire a received signal having a high signal value. Accordingly, it is possible to improve reception sensitivity.

In the ultrasonic transducer according to the application example, it is preferable that the support substrate has a wiring portion, which is connected to the suppressing portion, on a surface facing the vibration film.

In the application example with this configuration, the suppressing portion is connected to the wiring portion provided on the surface of the support substrate facing the vibration film. Therefore, by bonding the connection wiring line connected to the vibration element and the wiring portion to each other through the suppressing portion as described above, these can be electrically connected to each other.

In the ultrasonic transducer according to the application example, it is preferable that the support substrate includes a penetrating electrode that penetrates the support substrate in a thickness direction to connect the wiring portion and a circuit board, on which a circuit for controlling the vibration element is provided, to each other.

In the application example with this configuration, the penetrating electrode is further provided on the support substrate, and the penetrating electrode is connected to the wiring portion. Therefore, by connecting the penetrating electrode, which is exposed on the surface of the support substrate not facing the vibration film, to the circuit board, the vibration element can be easily electrically connected to the circuit board without using an FPC or the like.

An ultrasonic probe according to this application example includes: an ultrasonic transducer; and a housing in which the ultrasonic transducer is housed. The ultrasonic transducer includes: a substrate in which an opening is formed; a vibration film that is provided on the substrate so as to close the opening; a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film; a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.

The ultrasonic probe according to this application example includes the housing in which the ultrasonic transducer is housed as described above. As described above, the ultrasonic transducer has high ultrasonic wave transmission

or reception efficiency, and is excellent in mass productivity. Therefore, it is possible to provide an ultrasonic probe having high ultrasonic wave transmission or reception efficiency and excellent in mass productivity.

An ultrasonic apparatus according to this application example includes: an ultrasonic transducer; and a control unit that controls the ultrasonic transducer. The ultrasonic transducer includes: a substrate in which an opening is formed; a vibration film that is provided on the substrate so as to close the opening; a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film; a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.

The ultrasonic apparatus according to this application example includes the ultrasonic transducer described above and the control unit that controls the ultrasonic transducer. As described above, since the ultrasonic transducer is excellent in mass productivity, it is also possible to improve the mass productivity in the ultrasonic apparatus. In addition, by controlling the ultrasonic transducer using the control unit, ultrasonic wave transmission processing or ultrasonic wave receiving processing in the ultrasonic transducer can be performed with high efficiency.

An ultrasonic transducer manufacturing method according to this application example includes: forming, on a vibration film of a substrate in which the vibration film is provided, a plurality of vibration elements for performing at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film; forming a suppressing portion, which is formed of a resin material for suppressing transmission of vibration of the vibration film, on a surface of the vibration film not facing the substrate and between the adjacent vibration elements in a plan view along a thickness direction of the vibration film; making a support substrate, which has a surface facing the vibration film as a flat surface, face the surface of the vibration film not facing the substrate and bonding the other end portion of the suppressing portion, which is on an opposite side to one end portion of the suppressing portion connected to the vibration film, to the support substrate by heating; and forming an opening in the substrate such that the plurality of vibration elements are disposed at positions where the vibration film and the opening overlap each other in the plan view.

In this application example, after forming the vibration elements on the vibration film of the substrate in which the vibration film is provided, the suppressing portion formed of a resin material is formed between the vibration elements on the vibration film. Then, in the bonding step, the suppressing portion formed of a resin material is heated to be bonded to the support substrate. Then, an opening is formed in the substrate.

In such a manufacturing method, since the suppressing portion formed of a resin material is formed on the vibration film, it is possible to form the suppressing portion between the vibration elements with high accuracy by photolithography or the like. Therefore, it is possible to form a vibration

region at the desired position of the vibration film. Accordingly, it is possible to suppress a reduction in the efficiency of ultrasonic wave transmission and reception due to the positional shift between each vibration region and the vibration element. In addition, since the suppressing portion is bonded to the support substrate by heat bonding in the bonding step, it is not necessary to use an adhesive or the like. Accordingly, it is possible to improve the manufacturing efficiency. In addition, in the opening forming step, it is sufficient to form an opening over a plurality of vibration elements. Therefore, since it is possible to make the size of the opening relatively large, it is possible to further improve the manufacturing efficiency.

A vibration device according to this application example includes: a vibration film that has a predetermined thickness and is able to vibrate in a thickness direction; a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and a suppressing portion that is provided along a vibration region in the vibration film and suppresses transmission of vibration of the vibration region of the vibration film to a region other than the vibration region. The suppressing portion is formed of a resin material, and is bonded to the vibration film and the support substrate.

In this application example, since the suppressing portion formed of a resin material is provided along the vibration region of the vibration film as described above, it is possible to suppress the transmission of vibration to a region other than the vibration region. Accordingly, it is possible to transmit and receive ultrasonic waves with high efficiency. In addition, since the suppressing portion formed of a resin material can be formed on the vibration film easily and highly accurately by, for example, photolithography, the suppressing portion can be easily bonded to the vibration film or to the support substrate by, for example, heat pressure bonding. Therefore, it is possible to improve the manufacturing efficiency of the ultrasonic transducer.

BRIEF DESCRIPTION OF THE DRAWINGS

The invention will be described with reference to the accompanying drawings, wherein like numbers reference like elements.

FIG. 1 is a diagram showing the schematic configuration of an ultrasonic measurement apparatus of a first embodiment.

FIG. 2 is a block diagram showing the schematic configuration of the ultrasonic measurement apparatus of the first embodiment.

FIG. 3 is a plan view when a base portion in an ultrasonic sensor of the first embodiment is viewed from the sealing plate side.

FIG. 4 is an enlarged plan view of a part of FIG. 3.

FIG. 5A is a sectional view of an ultrasonic sensor taken along the line A-A of FIG. 4, FIG. 5B is a sectional view of an ultrasonic sensor taken along the line B-B of FIG. 4, and FIG. 5C is a sectional view of an ultrasonic sensor taken along the line C-C of FIG. 4.

FIG. 6A is a diagram showing a displacement profile of a vibration film in the first embodiment, FIG. 6B is a diagram showing a displacement profile of a known vibration film (a vibration region is formed by only a partition wall), and FIG. 6C is a diagram showing a displacement profile in a case where no suppressing portion is provided.

FIG. 7 is a flowchart showing a method of manufacturing the ultrasonic sensor of the first embodiment.

FIGS. 8A to 8F are diagrams showing the state of the ultrasonic sensor in each step of FIG. 7.

FIG. 9 is a plan view when a base portion in an ultrasonic sensor of a second embodiment is viewed from the sealing plate side.

FIGS. 10A and 10B are sectional views schematically showing the ultrasonic sensor of the second embodiment.

FIG. 11 is a plan view when a base portion in an ultrasonic sensor in a modification example is viewed from the sealing plate side.

DESCRIPTION OF EXEMPLARY EMBODIMENTS

First Embodiment

Hereinafter, a first embodiment will be described.

FIG. 1 is a diagram showing the schematic configuration of an ultrasonic measurement apparatus 1 of the first embodiment. FIG. 2 is a block diagram showing the schematic configuration of the ultrasonic measurement apparatus 1 of the present embodiment.

As shown in FIG. 1, the ultrasonic measurement apparatus 1 (ultrasonic apparatus) of the present embodiment includes an ultrasonic probe 2 and a control device 10 (control unit) that is electrically connected to the ultrasonic probe 2 through a cable 3.

In the ultrasonic measurement apparatus 1, the ultrasonic probe 2 is brought into contact with the surface of the living body (for example, a human body), ultrasonic waves are transmitted to the inside of the object (for example, a living body) from the ultrasonic probe 2, ultrasonic waves reflected by the organ in the living body are received by the ultrasonic probe 2, and, for example, an internal tomographic image in the living body is obtained or the state of the organ in the body (for example, a blood flow) is measured based on the received signal.

Configuration of an Ultrasonic Probe

The ultrasonic probe 2 includes a housing 21 (refer to FIG. 1), an ultrasonic sensor 22 provided in the housing 21, and a circuit board 23 on which a driver circuit for controlling the ultrasonic sensor 22 and the like are provided.

As shown in FIG. 1, the housing 21 is formed in a rectangular box shape in a plan view, for example. A sensor window 21B is provided on one surface (sensor surface 21A) perpendicular to the thickness direction, so that a part of the ultrasonic sensor 22 (ultrasonic transducer) housed therein is exposed. A passage hole of the cable 3 is provided in a part (in the example shown in FIG. 1, on a side surface) of the housing 21, and the cable 3 is connected to the circuit board 23 in the housing 21 through the passage hole. In addition, a gap between the cable 3 and the passage hole is filled with, for example, a resin material. Accordingly, waterproofness is ensured.

In the present embodiment, an example of the configuration is shown in which the ultrasonic probe 2 and the control device 10 are connected to each other using the cable 3. However, without being limited thereto, for example, the ultrasonic probe 2 and the control device 10 may be connected to each other by wireless communication, or various components of the control device 10 may be provided in the ultrasonic probe 2.

Configuration of an Ultrasonic Sensor

FIG. 3 is a plan view when a base portion 41 in the ultrasonic sensor 22 is viewed from a sealing plate 42 side. FIG. 4 is an enlarged plan view of a part of FIG. 3. FIGS. 5A to 5C are sectional views of the ultrasonic sensor 22.

FIG. 5A is a sectional view taken along the line A-A of FIG. 4, FIG. 5B is a sectional view taken along the line B-B of FIG. 4, and FIG. 5C is a sectional view taken along the line C-C of FIG. 4.

As shown in FIG. 4, the ultrasonic sensor 22 (ultrasonic transducer) includes the base portion 41, the sealing plate 42 (support substrate), a suppressing portion 43, an acoustic matching layer 44, and an acoustic lens 45.

Configuration of a Base Portion

As shown in FIGS. 5A to 5C, the base portion 41 includes a substrate 411, a vibration film 412 laminated on the substrate 411, and a piezoelectric element 413 (vibration element) laminated on the vibration film 412.

Here, as shown in FIG. 3, in a plan view of the base portion 41 from the thickness direction, an array region Ar1 is provided at the center of the base portion 41, and a plurality of piezoelectric elements 413 are arranged in an array in the array region Ar1.

In addition, as shown in FIGS. 5A to 5C, the base portion 41 includes the substrate 411 in which an opening 411A is formed, the vibration film 412 provided on the back side of the substrate 411 so as to close the opening 411A, and the piezoelectric element 413 provided on a side of the vibration film 412 not facing the opening 411A.

Configuration of a Substrate

The substrate 411 is, for example, a semiconductor substrate formed of silicon (Si). In the array region Ar1 of the substrate 411, the opening 411A is provided as described above. The substrate 411 includes a partition wall 411B surrounding the opening 411A. As shown in FIGS. 3 to 5C, in a plan view of the vibration film 412 from the film thickness direction (Z direction), the opening 411A has a shape with a high aspect ratio in which the length along a second direction (Y direction) is much larger than the length along a first direction (X direction), for example, a shape with an aspect ratio of 1:70. On the other hand, in the piezoelectric element 413, an active portion 413A in which a lower electrode 414, a piezoelectric layer 415, and an upper electrode 416 are laminated has a shape with a low aspect ratio in which the length along the X direction is close to the length along the Y direction, for example, a shape with an aspect ratio of approximately 1. Taking into consideration that the distortion of the active portion 413A in the film thickness direction is increased, it can be said theoretically that it is the most ideal that the aspect ratio of the active portion 413A is 1. However, the aspect ratio of the active portion 413A may be a value larger than 1. For one opening 411A, a plurality of active portions 413A are arranged along the Y direction, for example.

Configuration of a Vibration Film

The vibration film 412 is a laminate formed of a silicon oxide (SiO₂) layer and a zirconium oxide (ZrO₂) layer, for example. The vibration film 412 is supported by the partition wall 411B of the substrate 411. The vibration film 412 closes the opening 411A provided in the substrate 411 as described above.

The thickness of the vibration film 412 is sufficiently smaller than the thickness of the substrate 411. In the present embodiment, in a region overlapping the opening 411A of the vibration film 412 that closes the opening 411A, a plurality of regions (vibration regions Ar2) surrounded by the partition wall 411B and the suppressing portion 43, which will be described later, are arranged along the Y direction. In the present embodiment, one active portion 413A is arranged in each of the vibration regions Ar2. The vibration region Ar2 is vibrated by the driving of the active portion 413A. Then, ultrasonic waves are transmitted, and

the vibration region Ar2 vibrates. Then, a potential difference is generated in the piezoelectric layer 415 of the active portion 413A, and a detection signal is output. As a result, it is possible to detect the received ultrasonic waves.

Configuration of a Piezoelectric Element

The piezoelectric element 413 is provided on the vibration film 412, and is formed by the lower electrode 414, the piezoelectric layer 415, and the upper electrode 416. As described above, a portion in which the lower electrode 414, the piezoelectric layer 415, and the upper electrode 416 overlap each other in the film thickness direction (Z direction) functions as the active portion 413A of the piezoelectric element 413.

On the vibration film 412 or the piezoelectric element 413, an insulating layer 417 (protective layer) formed of, for example, alumina is formed.

The lower electrode 414 is patterned with a predetermined width in the X direction, and extends along the Y direction to be continuously provided over a plurality of active portions 413A. That is, the lower electrode 414 is formed by a lower electrode main body portion 414A, which forms a part of the active portion 413A, and a lower connection wiring line 414B that connects the lower electrode main body portions 414A adjacent to each other in the Y direction.

End portions of the plurality of lower electrodes 414 (in FIG. 3, for example, three lower electrodes 414) arranged in the Y direction are connected to each other. For example, the end portions of the plurality of lower electrodes 414 are drawn out to the peripheral ends of the substrate 411 on the $\pm Y$ sides, and a lower electrode terminal 414P is provided in a part (for example, a distal end) thereof. Although details will be described later, in the present embodiment, a block B of 1 channel (ch) is formed by the piezoelectric element 413 connected to the lower electrodes 414 that are connected to each other, and a plurality of blocks B are arranged in the X direction.

The upper electrode 416 is patterned with a predetermined width in the Y direction, and extends along the X direction to be continuously provided over a plurality of active portions 413A. That is, the upper electrode 416 is formed by an upper electrode main body portion 416A that forms a part of the active portion 413A, an upper connection wiring line 416B that connects the upper electrode main body portions 416A adjacent to each other in the X direction, and a common wiring line 416C that connects the upper connection wiring lines 416B to each other.

For example, as shown in FIG. 3, the common wiring line 416C is formed along the Y direction between the adjacent blocks B, and the common wiring line 416C is drawn out to the peripheral ends of the substrate 411 on the $\pm Y$ sides. An upper electrode terminal 416P is provided in a part (for example, a distal end) of the common wiring line 416C. Although an example in which the common wiring line 416C is disposed between the blocks B is shown in the present embodiment, for example, the end portions of the upper electrodes 416 may be connected to each other.

The piezoelectric layer 415 is disposed in a matrix corresponding to the intersection position of the lower electrode 414 and the upper electrode 416 in a plan view seen from the thickness direction of the vibration film 412.

Materials of the lower electrode 414 or the upper electrode 416 are not limited as long as the materials are conductive materials. As examples of the material of the lower electrode 414 or the upper electrode 416, it is possible to use metal materials such as platinum (Pt), iridium (Ir), gold (Au), aluminum (Al), copper (Cu), titanium (Ti), and stainless steel, tin oxide based conductive materials such as

indium tin oxide (ITO) and fluorine doped tin oxide (FTC), zinc oxide based conductive materials, oxide conductive materials such as ruthenium acid strontium (SrRuO_3), nickel lanthanum (LaNiO_3), and earth doped strontium titanate, and a conductive polymer.

Typically, a composite oxide having a lead zirconate titanate (PZT) based perovskite structure (ABO_3 -type structure) can be used as the piezoelectric layer **415**. According to this, it becomes easy to ensure the amount of displacement of the piezoelectric element **413**.

In addition, a composite oxide having a perovskite structure (ABO_3 -type structure) containing no lead can be used as the piezoelectric layer **415**. According to this, the ultrasonic sensor **22** can be realized using a non-lead-based material having a less influence on the environment.

As such a non-lead-based piezoelectric material, for example, a BFO-based material containing bismuth ferrite (BFO ; BiFeO_3) can be mentioned. In BFO, Bi is located at A site, and iron (Fe) is located at B site. Other elements may be added to BFO. For example, at least one element selected from ferrate manganese (Mn), aluminum (Al), lanthanum (La), barium (Ba), titanium (Ti), cobalt (Co), cerium (Ce), samarium (Sm), chromium (Cr), potassium (K), lithium (Li), calcium (Ca), strontium (Sr), vanadium (V), niobium (Nb), tantalum (Ta), molybdenum (Mo), tungsten (W), nickel (Ni), zinc (Zn), praseodymium (Pr), neodymium (Nd), and Yttrium (Eu) may be added to sodium potassium niobate (KNN ; KNaNbO_3).

In addition, as another example of the non-lead-based piezoelectric material, a KNN-based material containing sodium potassium niobate (KNN) can be mentioned. Other elements may be added to KNN. For example, at least one element selected from manganese (Mn), lithium (Li), barium (Ba), calcium (Ca), strontium (Sr), zirconium (Zr), titanium (Ti), bismuth (Bi), tantalum (Ta), antimony (Sb), iron (Fe), cobalt (Co), silver (Ag), magnesium (Mg), zinc (Zn), copper (Cu), vanadium (V), chromium (Cr), molybdenum (Mo), tungsten (W), nickel (Ni), aluminum (Al), silicon (Si), lanthanum (La), cerium (Ce), praseodymium (Pr), neodymium (Nd), promethium (Pm), samarium (Sm), and europium (Eu) may be added to KNN.

Examples of a composite oxide having a perovskite structure include a composite oxide deviating from the stoichiometric composition due to deficiency and excess or a composite oxide in which some elements have been replaced with other elements. That is, as long as the perovskite structure can be taken, not only inevitable deviation of composition due to lattice mismatch, oxygen deficiency, or the like but also substitution of some elements is allowed.

Configuration of a Sealing Plate and a Suppressing Portion

As shown in FIGS. **5A** to **5C**, the sealing plate **42** is disposed so as to face the vibration film **412** of the base portion **41**.

The sealing plate **42** has a flat opposite surface **421** facing the vibration film **412**, and the opposite surface **421** is bonded to the vibration film **412** of the base portion **41** by the suppressing portion **43** for suppressing the vibration of the vibration film **412**. Since the sealing plate **42** is bonded to the base portion **41** by the suppressing portion **43**, a space **S** around the piezoelectric element **413** is sealed.

In addition, since the material or thickness of the sealing plate **42** affects the frequency characteristics of the ultrasonic sensor **22**, it is preferable to set the material or thickness of the sealing plate **42** based on the center frequency of ultrasonic waves transmitted and received by the ultrasonic sensor **22**.

In the present embodiment, in the sealing plate **42**, a through hole (not shown) is provided so as to face the lower electrode terminal **414P** or the upper electrode terminal **416P**. Through the through hole, a wiring portion (for example, an FPC) is connected to the lower electrode terminal **414P** or the upper electrode terminal **416P** of the base portion **41**.

The suppressing portion **43** is formed of a resin material, and is bonded to both the vibration film **412** of the base portion **41** and the sealing plate **42** as described above. The suppressing portion **43** is formed on the vibration film **412** by, for example, sputtering and is patterned, and is then bonded to the sealing plate **42** by heat bonding.

As shown in FIGS. **3** to **5C**, the suppressing portion **43** is disposed at the midpoint position of the adjacent active portions **413A** between the active portions **413A** of the piezoelectric elements **413** arranged in the Y direction, and is formed so as to extend along the X direction.

That is, the partition wall **411B** is present between each vibration region **Ar2** of the vibration film **412** and the vibration region **Ar2** adjacent thereto in the X direction. Accordingly, as shown in FIGS. **5A** and **5B**, sides of each vibration region **Ar2** parallel to the Y direction (portions on both outer sides of the sides of each active portion **413A** parallel to the Y direction) are fixed by the partition wall **411B**. On the other hand, as shown in FIG. **5C**, in the Y direction, between the adjacent vibration regions **Ar2**, there is a portion where the partition wall **411B** is not present. The suppressing portion **43** is provided in the portion. In addition, on sides of each vibration region **Ar2** parallel to the X direction (portions on both outer sides of the sides of each active portion **413A** parallel to the X direction), the vibration film **412** is fixed by the suppressing portion **43** or the partition wall **411B** of the substrate **411**.

Configuration of an Acoustic Matching Layer and an Acoustic Lens

As shown in FIGS. **5A** to **5C**, the acoustic matching layer **44** is provided on the working surface (not facing the sealing plate **42**) side of the base portion **41**. Specifically, the acoustic matching layer **44** is filled in the opening **411A** of the base portion **41**, and is formed in a predetermined thickness from the working surface side of the substrate **411**.

The acoustic lens **45** is provided on the acoustic matching layer **44**, and is exposed to the outside from the sensor window **21B** of the housing **21** as shown in FIG. **1**.

Due to the acoustic matching layer **44** or the acoustic lens **45**, ultrasonic waves transmitted from the ultrasonic sensor **22** efficiently propagate toward the living body that is a measurement target, and ultrasonic waves reflected from the inside of the living body efficiently propagate toward the ultrasonic sensor **22**. For this reason, the acoustic impedance of the acoustic matching layer **44** and the acoustic lens **45** is set to the intermediate acoustic impedance between the acoustic impedance of the ultrasonic sensor **22** and the acoustic impedance of the living body.

Transmission and Reception of Ultrasonic Waves by an Ultrasonic Sensor

In the ultrasonic sensor **22** described above, the upper electrodes **416** of the respective piezoelectric elements **413** arranged in the array region **Ar1** are connected to each other. Therefore, the upper electrodes **416** of the respective piezoelectric elements **413** arranged in the array region **Ar1** have the same electric potential. Assuming that the piezoelectric elements **413** along the Y direction are a group of piezoelectric elements, the lower electrodes **414** of the piezoelectric elements **413** included in three groups of piezoelectric elements along the X direction are connected to each other.

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Therefore, the lower electrodes **414** of the piezoelectric elements **413** included in three groups of piezoelectric elements along the X direction have the same electric potential. In the present embodiment, a plurality of blocks B are arranged along the X direction with the three groups of piezoelectric elements as the block B of 1 channel (ch).

Then, in the present embodiment, at the time of transmission (driving processing) of ultrasonic waves, a driving signal SIG is input to each lower electrode terminal **414P**, and a common bias signal COM is input to each upper electrode terminal **416P** from the circuit board **23**. By controlling the strength or the input timing of the driving signal input to each lower electrode terminal **414P**, a potential difference is generated between the lower electrode **414** and the upper electrode **416** of each active portion **413A** included in each block B, and the piezoelectric layer **415** vibrates. Accordingly, the vibration region Ar2 of the vibration film **412** is also driven to vibrate. As a result, ultrasonic waves are generated.

At the time of reception (detection processing) of ultrasonic waves, a common bias signal is input to the upper electrode terminal **416P** from the circuit board **23**. Then, ultrasonic waves from an object are input to the ultrasonic sensor **22**, and each vibration region Ar2 of the vibration film **412** is driven to vibrate. Accordingly, a potential difference is generated between the lower electrode **414** and the upper electrode **416**. Then, a detection signal corresponding to the deflection of the piezoelectric element **413** is output to the circuit board **23** from the lower electrode terminal **414P** corresponding to each block B.

Since the ease of deflection deformation of the piezoelectric element **413** changes with the material or thickness of the piezoelectric element **413** or the vibration film **412** and the arrangement position or size of the vibration region Ar2, it is possible to appropriately adjust the material or thickness of the piezoelectric element **413** or the vibration film **412** and the arrangement position or size of the vibration region Ar2 according to the application or usage mode.

In addition, using a resonance frequency unique to each material, the resonance frequency and the frequency of a charge signal applied to the piezoelectric element **413** may be made to match or substantially match each other to cause the deflection deformation of the piezoelectric element **413** using resonance.

Displacement of a Vibration Film at the Time of Transmission and Reception of Ultrasonic Waves

FIG. 6A is a diagram showing a displacement profile of a vibration film in the present embodiment, FIG. 6B is a diagram showing a displacement profile of a known vibration film (in the related art, a vibration region is formed by only a partition wall), and FIG. 6C is a diagram showing a displacement profile in a case where no suppressing portion is provided in the present embodiment.

As described above, in the present embodiment, when transmitting ultrasonic waves from the ultrasonic sensor **22** and when receiving ultrasonic waves, each vibration region Ar2 of the vibration film **412** is displaced.

In the case of the displacement profile of the vibration region Ar2 of the present embodiment, as shown in FIG. 6A, the center of the vibration region Ar2 (the center of the active portion **413A**) is the center of the displacement, and large displacement (distortion in the film thickness direction) occurs in the vibration region Ar2. This is almost the same as in the case shown in FIG. 6B in which a substrate having an opening with a low aspect ratio is used (case where the vibration region Ar2 is formed by only the partition wall **411B**). On the other hand, in a case where the

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suppressing portion **43** is not provided, as shown in FIG. 6C, the center of the displacement moves to the outside of the active portion **413A**. Accordingly, the displacement (distortion in the film thickness direction) of the active portion **413A** is considerably small.

From FIGS. 6A to 6C, it can be seen that, in a case where there is a portion where the partition wall **411B** is not present between the adjacent active portions **413A** (midpoint position), it is possible to suppress the vibration of the vibration film **412** by providing the suppressing portion **43** in the portion and pressing the vibration film **412** against the substrate **411** from the side opposite to the opening **411A**. That is, it can be seen that the vibration range of the vibration film **412** is restricted by the suppressing portion **43**. In addition, in the present embodiment, although the opening **411A** has a high aspect ratio, the same displacement as in the case where the opening **411A** has a low aspect ratio is obtained. Therefore, it can be seen that the effect of suppressing vibration using the suppressing portion **43** is enormous.

Configuration of a Circuit Board

As shown in FIG. 2, the circuit board **23** has a substrate terminal portion **231** connected to the lower electrode terminal **414P** or the upper electrode terminal **416P** provided in the base portion **41**. In addition, a driver circuit for driving the ultrasonic sensor **22** and the like are provided on the circuit board **23**. Specifically, as shown in FIG. 2, the circuit board **23** includes a selection circuit **232**, a transmission circuit **233**, a receiving circuit **234**, and the like.

The selection circuit **232** switches a transmission connection for connecting the ultrasonic sensor **22** and the transmission circuit **233** and a reception connection for connecting the ultrasonic sensor **22** and the receiving circuit **234** based on the control of the control device **10**.

When switching to the transmission connection is made by the control of the control device **10**, the transmission circuit **233** outputs a signal, which indicates the transmission of ultrasonic waves, to the ultrasonic sensor **22** through the selection circuit **232**.

When switching to the reception connection is made by the control of the control device **10**, the receiving circuit **234** outputs a detection signal, which is input from the ultrasonic sensor **22** through the selection circuit **232**, to the control device **10**. The receiving circuit **234** is configured to include, for example, a low noise amplifier circuit, a voltage controlled attenuator, a programmable gain amplifier, a low pass filter, and an A/D converter. The receiving circuit **234** performs various kinds of signal processing, such as the conversion of a received signal to a digital signal, removal of noise components, and amplification to a desired signal level, and then outputs the received signal after the processing to the control device **10**.

Configuration of a Control Device

As shown in FIG. 2, the control device **10** is configured to include, for example, an operating unit **11**, a display unit **12**, a storage unit **13**, and a calculation unit **14**. As examples of the control device **10**, a terminal device, such as a tablet terminal, a smartphone, or a personal computer, may be used, or a dedicated terminal device for operating the ultrasonic probe **2** may be used.

The operating unit **11** is a user interface (UI) used when the user operates the ultrasonic measurement apparatus **1**. For example, the operating unit **11** can be configured to include a touch panel provided on the display unit **12**, operation buttons, a keyboard, a mouse, or the like.

The display unit **12** is formed using, for example, a liquid crystal display, and displays an image thereon.

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The storage unit **13** stores various programs and various kinds of data for controlling the ultrasonic measurement apparatus **1**.

The calculation unit **14** is configured to include, for example, an arithmetic circuit, such as a central processing unit (CPU), and a storage circuit, such as a memory. The calculation unit **14** reads various programs stored in the storage unit **13** and executes the various programs, thereby performing the generation of a transmission signal and the control of output processing for the transmission circuit **233** and performing received signal frequency setting, gain setting, or the like for the receiving circuit **234**.

Method of Manufacturing an Ultrasonic Sensor

Next, a method of manufacturing the above ultrasonic sensor **22** will be described.

FIG. **7** is a flowchart showing each step in the manufacturing of the ultrasonic sensor **22** of the present embodiment. FIGS. **8A** to **8F** are diagrams schematically showing the ultrasonic sensor **22** in each step.

In order to manufacture the ultrasonic sensor **22**, as shown in FIG. **7**, a substrate preparation step **S1**, an element forming step **S2**, a suppressing portion forming step **S3**, a bonding step **S4**, and an opening forming step **S5** are performed.

In the substrate preparation step **S1**, first, one surface side of the substrate **411** formed of Si is thermally oxidized to form an SiO₂ layer that is a part of the vibration film **412**. Then, a Zr layer is formed on the SiO₂ layer, and the Zr layer is thermally oxidized to form a ZrO₂ layer. As a result, as shown in FIG. **8A**, the vibration film **412** is formed on the substrate **411**.

Then, the element forming step **S2** is performed.

In the element forming step **S2**, first, an electrode material for forming the lower electrode **414** is formed on the vibration film **412** by sputtering, for example. Then, a resist is applied on the lower electrode **414**, a resist pattern is formed by photolithography or the like, and the lower electrode **414** is patterned by etching, for example.

Then, the piezoelectric layer **415** is formed on the lower electrode **414**. The piezoelectric layer **415** is formed by a solution method using PZT, for example. For example, application processing for applying the PZT solution with a composition ratio of Zr:Ti=52:48 on the vibration film **412** and the lower electrode **414** and baking processing for baking the applied PZT solution under the conditions of, for example, pre-baking of 400° C. and RTA baking of 700° C. are performed multiple times, thereby obtaining a piezoelectric layer having a desired thickness. Then, the piezoelectric layer **415** is formed by patterning the formed piezoelectric layer by etching (ion milling).

After forming the piezoelectric layer **415**, an electrode material for forming the upper electrode **416** is applied on the vibration film **412**. Then, in the same manner as for the lower electrode **414**, a resist pattern is formed and patterned by etching or the like.

Thus, as shown in FIG. **8B**, the piezoelectric element **413** configured to include the lower electrode **414**, the piezoelectric layer **415**, and the upper electrode **416** is formed on the vibration film **412**. In the present embodiment, the thickness of the active portion **413A** is set to about 1.3 μm.

After forming the piezoelectric element **413**, the insulating layer **417** that covers the vibration film **412** and the piezoelectric element **413** is formed as a protective layer. The insulating layer **417** on the lower electrode terminal **414P** and the upper electrode terminal **416P** is removed by etching or the like.

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Then, the suppressing portion **43** is formed on the vibration film **412** (on the insulating layer **417**).

In forming the suppressing portion **43**, as shown in FIG. **8C**, for example, a photosensitive resin material (photoresist) is applied onto the vibration film **412** by spin coating, sputtering, or the like. Then, on the vibration film **412**, a mask pattern along the X direction is formed between the active portions **413A**. A region other than the mask is removed by photolithography. As a result, as shown in FIG. **8D**, the suppressing portion **43** formed of a resin material is formed on the vibration film **412**.

Then, the bonding step **S4** is performed. In the bonding step **S4**, the substrate **411** is placed on, for example, a hot plate (not shown) so that the vibration film **412** faces upward (side opposite to the hot plate). In addition, the sealing plate **42** is placed on the vibration film **412**, and the sealing plate **42** is pressed toward the substrate **411** side with predetermined pressure. Then, the suppressing portion **43** that is a resin material is softened. As a result, as shown in FIG. **8E**, an end portion of the suppressing portion **43** not facing the vibration film **412** is heated to be bonded (melted to be bonded) to the sealing plate **42**. The thickness of the suppressing portion **43** along the Z direction in the bonding state is, for example, about 1.5 μm, which is sufficiently larger than the width of the suppressing portion **43** in the Y direction. Therefore, for example, in the ultrasonic sensor **22** for living body, the suppressing portion **43** is not deformed or crushed even if normal pressure is applied. As a result, it is possible to suppress the deformation of the vibration film **412** and the like.

In the present embodiment, the suppressing portion **43** of a resin material is formed on the vibration film **412** by photolithography. In such a case, for example, compared with a case where the suppressing portion **43** is provided on the sealing plate **42** side, it is possible to improve the positional accuracy of the suppressing portion **43**.

That is, in a case where the suppressing portion **43** is provided on the sealing plate **42** and the distal end is bonded to the vibration film **412**, it is necessary to perform alignment so that the suppressing portion **43** is located at the intermediate position of the active portion **413A** of the piezoelectric element **413**. When the suppressing portion **43** is in contact with the active portion **413A**, the driving efficiency of the active portion **413A** is reduced. Accordingly, the sound pressure of ultrasonic waves is reduced in ultrasonic wave transmission processing, and reception sensitivity is reduced in ultrasonic wave reception processing. Even if the suppressing portion **43** is not in contact with the active portion **413A**, if the position is shifted, a deviation occurs in the shape or size of the vibration region **Ar2**. Accordingly, since it becomes difficult to transmit and receive ultrasonic waves having a desired frequency, the driving efficiency of the active portion **413A** is reduced, and the efficiency in ultrasonic wave transmission and reception is also reduced.

In contrast, in the present embodiment, the suppressing portion **43** is patterned on the vibration film **412** by photolithography as described above. Therefore, it is possible to form the suppressing portion **43** at an optimal position with respect to the active portion **413A** or the vibration region **Ar2**. That is, since it is possible to form the accurate ultrasonic sensor **22**, complicated alignment is not necessary. Therefore, it is possible to improve the manufacturing efficiency.

The suppressing portion **43** formed of a resin material can be easily bonded to the sealing plate **42** by heat bonding as described above. In a case where apart of the sealing plate

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42 is protruded to form the suppressing portion 43 or a case where the suppressing portion 43 is formed of a metal material or the like, it is necessary to bond the suppressing portion 43 to the vibration film 412 by separately applying an adhesive or the like. Accordingly, the time and effort in the bonding step are increased. In addition to the complication of alignment described above, there is a possibility that the adhesive will adhere to the active portion 413A. In contrast, in the present embodiment, the sealing plate 42 and the vibration film 412 can be bonded to each other easily.

Thus, after bonding the sealing plate 42 to the base portion 41, the opening forming step S5 is performed. In the opening forming step S5, from the surface of the substrate 411 not facing the vibration film 412, the opening 411A is formed by, for example, etching, as shown in FIG. 8F. Specifically, a mask is formed in a region other than the formation region of the opening 411A, and the opening 411A is formed using the SiO₂ layer of the vibration film 412 as an etching stopper. In the case of bonding the suppressing portion 43 and the sealing plate 42 to each other after forming the opening 411A, the vibration film 412 is deformed when the sealing plate 42 is pressed toward the base portion 41 side. In contrast, in the present embodiment, the opening 411A is formed after bonding the sealing plate 42 to the vibration film 412. Therefore, it is possible to suppress the deformation of the vibration film 412 due to pressing by the suppressing portion 43.

Then, the opening 411A of the substrate 411 is filled with the acoustic matching layer 44, and the acoustic lens 45 is further bonded thereto, thereby manufacturing the ultrasonic sensor 22 shown in FIGS. 5A to 5C and the like.

Effect of the Present Embodiment

The ultrasonic measurement apparatus 1 of the present embodiment includes the ultrasonic probe 2, in which the ultrasonic sensor 22 for transmitting and receiving ultrasonic waves is disposed in the housing 21, and the control device 10 for controlling the ultrasonic sensor 22. The ultrasonic sensor 22 includes the substrate 411 having the opening 411A, the vibration film 412 that closes the opening 411A, the piezoelectric element 413 provided on the vibration film 412, and the sealing plate 42 that has the opposite surface 421, which is a flat surface facing the vibration film 412, and supports the vibration film 412. In addition, a plurality of piezoelectric elements 413 (active portions 413A) are provided at positions overlapping the opening 411A in a plan view, and the suppressing portion 43 formed of a resin material for suppressing the transmission of vibration of the vibration film 412 is provided between the adjacent active portions 413A.

In such a configuration, the vibration film 412 is divided into a plurality of vibration regions Ar2 by the partition wall 411B and the suppressing portion 43, and the active portion 413A of the piezoelectric element 413 is located at the center of each vibration region Ar2. Accordingly, even in a case where the opening 411A is large, the aspect ratio of each vibration region Ar2 can be reduced to a low aspect ratio.

In addition, as shown in FIGS. 6A to 6C, transmission of vibration of each vibration region Ar2 to a region (for example, the adjacent vibration region Ar2) other than the vibration region Ar2 is suppressed by the suppressing portion 43, and the amount of distortion in the thickness direction is increased at the center position of each vibration region Ar2 where the active portion 413A is provided. Therefore, high-output (large sound pressure) ultrasonic waves can be output when transmitting ultrasonic waves,

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and reception sensitivity can be improved when receiving ultrasonic waves (efficiency of transmission and reception of ultrasonic waves is improved).

In addition, for example, compared with a case where one active portion 413A is disposed for one opening 411A, it is possible to increase the size of the opening 411A. Accordingly, since it is easy to form the opening 411A, it is possible to improve the mass productivity of the ultrasonic sensor 22.

The suppressing portion 43 formed of such a resin material can be easily formed by, for example, photolithography, and can be easily bonded to the sealing plate 42 by heat bonding. Accordingly, since it is possible to further improve the manufacturing efficiency of the ultrasonic sensor 22, it is possible to further improve the mass productivity of the ultrasonic sensor 22.

In the present embodiment, after the substrate preparation step S1 and the element forming step S2, in the suppressing portion forming step, the suppressing portion 43 is formed by forming a photosensitive resin material layer on the vibration film 412 and patterning the photosensitive resin material layer by photolithography. Therefore, since it is possible to further improve the manufacturing efficiency, it is also possible to improve the efficiency in ultrasonic wave transmission and reception of the ultrasonic sensor 22.

That is, in a configuration in which a protruding portion provided on the sealing plate side is bonded to the vibration as a suppressing portion, it is necessary to align the position of the protruding portion highly accurately with respect to the opening 411A or the active portion 413A so that the active portion 413A is located at the center position of the vibration region Ar2. For this reason, the manufacturing efficiency is reduced. In addition, if the position of the protruding portion is shifted, the vibration region Ar2 cannot be formed at a desired position. Accordingly, a positional shift between the active portion 413A and the center of the vibration region Ar2 where the amount of distortion in the film thickness direction is the greatest occurs. In this case, the efficiency in ultrasonic wave transmission and reception is reduced.

In addition, since it is necessary to bond the protruding portion with an adhesive, a step of transferring the adhesive to the vibration film 412 is further required. In this case, there is a possibility that the transferred adhesive will overflow to the piezoelectric element 413 side to come into contact with the piezoelectric element 413 at the time of bonding. This may inhibit the driving of the piezoelectric element 413.

In contrast, in the present embodiment, the suppressing portion 43 formed of a resin material is formed by photolithography in the above suppressing portion forming step S3, and the suppressing portion 43 and the sealing plate 42 are bonded to each other by heat bonding in the bonding step S4. In this case, since it is possible to omit the step of transferring an adhesive or the alignment step described above, the manufacturing efficiency is further improved to the same extent. In addition, since the suppressing portion 43 can be formed at a desired position with high accuracy by photolithography, it is possible to arrange the vibration region Ar2 at a desired position. As a result, it is possible to suppress a reduction in the efficiency of ultrasonic wave transmission and reception.

Second Embodiment

Next, a second embodiment will be described.

In the first embodiment described above, the lower electrode 414 and the upper electrode 416 extend to the lower

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electrode terminal **414P** and the upper electrode terminal **416P** provided in the outer peripheral portion of the substrate **411**, thereby being connected to the circuit board **23** at the lower electrode terminal **414P** and the upper electrode terminal **416P**, respectively. In contrast, the second embodiment is different from the first embodiment in that the lower electrode **414** and the upper electrode **416** are connected to the circuit board **23** through a suppressing portion.

FIG. 9 is a plan view showing the schematic configuration of a base portion of the ultrasonic sensor **22** of the present embodiment. FIG. 10A is a schematic sectional view of the ultrasonic sensor **22** along the longitudinal direction of a suppressing portion **43A** electrically connected to the lower electrode **414**, and FIG. 10B is a schematic sectional view of the ultrasonic sensor **22** along the longitudinal direction of the suppressing portion **43A** electrically connected to the upper electrode **416**. In the following explanation, components described previously are denoted by the same reference numerals, and the explanation thereof will be omitted or simplified.

As shown in FIG. 9, in the ultrasonic sensor **22** of the present embodiment, the active portions **413A** of a plurality of piezoelectric elements **413** are arranged in a matrix in the array region **Ar1**, and the piezoelectric elements **413** arranged in the Y direction are connected to each other by the lower electrode **414** continuous along the Y direction, in the same manner as in the first embodiment. The piezoelectric elements **413** arranged in the X direction are connected to each other by the upper electrode **416** continuous along the X direction. In the present embodiment, as shown in FIG. 9, the lower electrodes **414** are not connected to each other at their end positions. Accordingly, the lower electrode terminal **414P** is not provided. Similarly, since the upper electrodes **416** are not connected to each other at their end positions, the upper electrode terminal **416P** is not provided.

In the present embodiment, the suppressing portion **43A** is formed so as to extend in the X direction at the same position as in the first embodiment, that is, between the active portions **413A** of the adjacent piezoelectric elements **413**, thereby bonding the vibration film **412** and the sealing plate **42** to each other. The suppressing portion **43A** of the present embodiment is formed of a resin material containing a conductive filler mixed therein, and has conductivity.

In the present embodiment, the insulating layer **417** is not formed on a part of the lower electrode **414** (lower connection wiring line **414B**) or a part of the upper electrode **416** (common wiring line **416C**).

That is, the suppressing portion **43A** for electrically connecting the lower electrode **414** to the circuit board **23** is provided corresponding to each block B. Accordingly, since a part of the lower electrode **414** is in contact with the suppressing portion **43A**, the lower electrode **414** is electrically connected to the circuit board **23**. In addition, the suppressing portion **43A** for electrically connecting the upper electrode **416** to the circuit board **23** is provided. Accordingly, since a part of the upper electrode **416** is in contact with the suppressing portion **43A**, the upper electrode **416** is electrically connected to the circuit board **23**.

For example, the lower electrode **414** (lower connection wiring line **414B**) of the piezoelectric element **413** included in a first block **B1** (refer to FIG. 9) disposed in the array region **Ar1** forms a lower electrode conducting portion **414C** (refer to FIG. 10A), on which the insulating layer **417** is not formed, in a portion where a first suppressing portion **43A1** is laminated. Then, the first suppressing portion **43A1** is formed on the lower electrode conducting portion **414C** of the lower electrode **414**. Accordingly, the first suppressing

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portion **43A1** and the lower electrode **414** of the first block **B1** come into contact with each other to be electrically connected to each other.

The lower electrode **414** (lower connection wiring line **414B**) of the piezoelectric element **413** included in a second block **B2** at a different position from the first block **B1** forms a lower electrode conducting portion **414C**, on which the insulating layer **417** is not formed, in a portion where a second suppressing portion **43A2** is laminated. Then, the second suppressing portion **43A2** is formed on the lower electrode conducting portion **414C** of the lower electrode **414**. Accordingly, the second suppressing portion **43A2** and the lower electrode **414** of the second block **B2** come into contact with each other to be electrically connected to each other.

The same is true for the other blocks B, and the suppressing portion **43A** that is electrically connected corresponding to each block is present.

In the present embodiment, as in the first embodiment, the upper electrodes **416** of the respective piezoelectric elements **413** arranged in the array region **Ar1** are connected to each other by the upper connection wiring line **416B** and the common wiring line **416C**. Then, as shown in FIG. 10B, the common wiring line **416C** forms an upper electrode conducting portion **416D**, on which the insulating layer **417** is not formed, in a portion where a third suppressing portion **43A3** corresponding to the upper electrode **416** is laminated. Then, the third suppressing portion **43A3** is formed on the upper electrode conducting portion **416D**. Accordingly, each upper electrode **416** and the third suppressing portion **43A3** come into contact with each other to be electrically connected to each other.

On the other hand, as shown in FIGS. 10A and 10B, the sealing plate **42** has at least one through hole **422**, which passes through the sealing plate **42** in the film thickness direction, at a position facing each suppressing portion **43A**. A penetrating electrode **423** is inserted through the through hole **422**, so that the suppressing portion **43A** is brought into contact with (bonded to) one end of the penetrating electrode **423**. The other end of the penetrating electrode **423** is connected to the substrate terminal portion **231** provided on the circuit board **23** by, for example, a conductive member, such as solder.

In the suppressing portion **43A** (for example, the suppressing portion **43A1** or the suppressing portion **43A2** shown in FIG. 9) electrically connected to the lower electrode **414**, a position where the through hole **422** and the penetrating electrode **423** are provided is preferably a position where the lower electrode conducting portion **414C** is provided. In the present embodiment, the block B of 1 ch is formed by three groups of piezoelectric elements, and three lower electrode conducting portions **414C** arranged in the X direction with respect to one suppressing portion **43B** are provided. In this case, as shown in FIGS. 9 and 10A, it is preferable to provide the penetrating electrode **423** at a position facing the lower electrode conducting portion **414C** at the center (position overlapping the lower electrode conducting portion **414C** at the center in a plan view). In addition, the three penetrating electrodes **423** may be provided so as to face the three lower electrode conducting portions **414C**.

The same is true for the suppressing portion **43A** (**43A3**) electrically connected to the upper electrode **416**, a position where the through hole **422** and the penetrating electrode **423** are provided is preferably a position where the upper electrode conducting portion **416D** is provided. For example, in the present embodiment, as shown in FIG. 9, the

penetrating electrode **423** is provided at a position facing the upper electrode conducting portion **416D** (position overlapping the upper electrode conducting portion **416D** in a plan view) of the common wiring line **416C** at the center of the array region **Art**. In addition, a plurality of penetrating electrodes **423** may be provided so as to face the respective upper electrode conducting portions **416D**.

Effect of the Present Embodiment

In the ultrasonic sensor **22** of the present embodiment, the suppressing portion **43A** is formed of a resin material containing a conductive filler. The suppressing portion **43A** is provided longitudinally along the X direction between the adjacent active portions **413A**, and is connected to the lower electrode conducting portion **414C** of the lower electrode **414** connected to each active portion **413A** or the upper electrode conducting portion **416D** of the upper electrode **416**.

In such a configuration, for example, as in the first embodiment, the lower electrode **414** or the upper electrode **416** does not need to be drawn out to the lower electrode terminal **414P** or the upper electrode terminal **416P** of the outer peripheral portion of the substrate **411**. For this reason, the lower electrode **414** or the upper electrode **416** can be electrically connected to the circuit board **23** through the suppressing portion **43A**. Therefore, it is possible to simplify the wiring configuration. In addition, since a signal can be input to a position near the active portion **413A** when inputting a signal to each active portion **413A**, it is possible to suppress the influence of a voltage drop. As a result, it is possible to improve the efficiency of ultrasonic wave transmission and reception of the ultrasonic sensor **22**.

In the present embodiment, the sealing plate **42** includes the penetrating electrode **423** that penetrates in the plate thickness direction, and the suppressing portion **43A** is electrically connected by being bonded onto the penetrating electrode **423**. That is, the suppressing portion **43A** is connected to a wiring portion that is a surface of the penetrating electrode **423** facing the vibration film **412**. In such a configuration, it is not necessary to separately connect a lead wire, an FPC, or the like to the suppressing portion **43A**, and the lower electrode **414** or the upper electrode **416** and the penetrating electrode **423** can be electrically connected to each other through the suppressing portion **43A** just by bonding the suppressing portion **43A** to the sealing plate **42**.

In the present embodiment, the other end portion of the penetrating electrode **423** not facing the vibration film **412** is electrically connected to a terminal portion of the circuit board **23** that is disposed on a side of the sealing plate **42** not facing the base portion **41**. Thus, each piezoelectric element **413** can be easily electrically connected to the circuit board **23** without using an FPC or the like.

Modification Examples

The invention is not limited to the embodiments described above, but various modifications, improvements, and appropriate combinations of the respective embodiments may be made in a range where the object of the invention can be achieved.

In the first embodiment described above, an example is shown in which the block B of one channel is formed by three groups of piezoelectric elements. However, the invention is not limited thereto. For example, the block B of one channel may be formed by one group of piezoelectric

elements, or the block B of one channel may be formed by two or four or more groups of piezoelectric elements. The lower electrode **414** of each piezoelectric element **413** may have an independent terminal portion, so that each piezoelectric element **413** is independently driven. In addition, although the configuration has been exemplified in which a plurality of blocks B are arranged along the X direction, it is possible to adopt a configuration in which a plurality of blocks B are arranged along the Y direction, a configuration in which a plurality of blocks B are arranged in a matrix along the X and Y directions, and the like.

In the embodiment described above, the opening **411A** and the piezoelectric element **413** are formed so that all active portions **413A** arranged along the Y direction are included in a position overlapping one opening **411A** in a plan view. However, the invention is not limited thereto.

For example, “n” openings **411A** longitudinal in the Y direction may be arranged along the Y direction, and “m” active portions **413A** may be arranged side by side along the Y direction in a region overlapping each opening **411A**. In this case, “n×m” piezoelectric elements **413** arranged in the Y direction are connected to each other by the lower electrode **414**, thereby forming a group of piezoelectric elements.

In the embodiment described above, it is assumed that the active portion **413A** and the opening **411A** are rectangles (including squares) in a plan view. However, the shape of the active portion **413A** may not be a rectangle. The shape of the active portion **413A** may not be a perfect rectangle. For example, a shape that generally looks rectangular even though the corner is round or the side is somewhat uneven may be applied, or a quadrangle other than the rectangle, a polygon, a circle, or an ellipse may be applied.

In the embodiment described above, the suppressing portions **43** and **43A** are provided only in a portion where the partition wall **411B** is not present between the adjacent vibration regions **Ar2** (active portions **413A**), and are not provided in a portion where the partition wall **411B** is present. However, the suppressing portions **43** and **43A** may be provided in a portion where the partition wall **411B** is located. For example, the suppressing portions **43** and **43A** may be provided along edge portions (sides of $\pm Y$ side end portions) of the opening **411A** along the X direction or edge portions (sides of $\pm X$ side end portions) of the opening **411A** along the Y direction.

In the embodiment described above, an example is shown in which the opening **411A** is longitudinal in the Y direction and a plurality of active portions **413A** arranged in the Y direction are arranged in the opening **411A**. However, the active portions **413A** arranged in a matrix along the X and Y directions may be provided in the opening **411A**. In this case, the suppressing portion **43** is also disposed between the active portions **413A** adjacent to each other along the X direction. Therefore, it is possible to form the vibration region **Ar2** corresponding to each active portion **413A**.

In the second embodiment, an example is shown in which the penetrating electrode **423** is provided on the sealing plate **42**. However, for example, a wiring portion in contact with the suppressing portion **43A** (wiring portion not penetrating the sealing plate **42**) may be provided on the substrate surface of the sealing plate **42**. In this case, a circuit pattern connected to a wiring terminal portion may be formed on the surface of the sealing plate **42A**, and a part of the circuit pattern may be connected to the circuit board **23**.

In each of the embodiments described above, the suppressing portions **43** and **43A** that are continuous across both

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end portions of the base portion **41** along the X direction has been exemplified. However, the invention is not limited thereto.

FIG. **11** is a diagram showing the schematic configuration of a substrate in a modification example.

For example, as shown in FIG. **11**, the suppressing portion **43A** (or the suppressing portion **43**) may be provided between both end portions of one block B in the X direction in a plan view. In FIG. **11**, an example is shown in which the suppressing portion **43** is provided in units of the block B. However, the suppressing portion **43A** (or the suppressing portion **43**) may be provided in units of the opening **411A**.

In these configurations, between the adjacent blocks B, a bonding portion **46** that is longitudinal along the Y direction may be provided on the common wiring line **416C**. Since the bonding portion **46** can be formed of, for example, the same resin material as the suppressing portion **43A** (or the suppressing portion **43**), the bonding portion **46** can be formed simultaneously with the suppressing portion **43**. In this case, since the sealing plate **42** and the base portion **41** can be bonded to each other along the X direction by the suppressing portion **43A** and the sealing plate **42** and the base portion **41** can be bonded to each other along the Y direction by the bonding portion **46**, it is possible to further increase the bonding strength.

In the second embodiment, a configuration may be applied in which the suppressing portion **43A** or the bonding portion **46** is formed as shown in FIG. **11**. In this case, each lower connection wiring line **414B** that connects the active portions **413A** to each other can be used as the lower electrode conducting portion **414C**. For example, as shown in FIG. **11**, all the suppressing portions **43A** present in the first block B1 become the first suppressing portions **43A1** electrically connected to the lower electrode **414** of the first block B1. In addition, all the suppressing portions **43A** present in the second block B2 become the second suppressing portions **43A2** electrically connected to the lower electrode **414** of the second block B2. In this case, since a signal can be input and output at a position closer to each active portion **413A**, it is possible to further suppress the influence of a voltage drop.

For the upper electrode **416**, the bonding portion **46** may be formed of a resin material containing a conductive filler, and the upper electrode conducting portion **416D** may be provided at each intersection position between the upper connection wiring line **416B** and the common wiring line **416C**. In a case where the bonding portion **46** is formed over all the upper electrodes **416** arranged in the Y direction, the common wiring line **416C** does not need to be formed, and the upper electrodes **416** are connected to each other by the bonding portion **46** having conductivity.

In the embodiment described above, the piezoelectric element **413** in which the lower electrode **414**, the piezoelectric layer **415**, and the upper electrode **416** are laminated in the thickness direction of the vibration film **412** has been exemplified as a vibration element. However, the invention is not limited thereto. For example, on the one surface side of the piezoelectric layer perpendicular to the thickness direction, a pair of electrodes may be disposed so as to face each other. Alternatively, on the side surface of the piezoelectric layer along the thickness direction, electrodes may be disposed so as to interpose a piezoelectric layer therebetween.

Instead of using the piezoelectric layer, a vibration element may be used that includes a first electrode provided on the vibration film **412** and a second electrode (for example, disposed on the sealing plate **42**) facing the first electrode

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with an air gap interposed therebetween and that vibrates the vibration film **412** with electrostatic force or detects the vibration of the vibration film **412**.

In each of the embodiments described above, the ultrasonic sensor **22** (ultrasonic transducer) provided in the ultrasonic probe **2** of the ultrasonic measurement apparatus **1** that is an ultrasonic apparatus has been exemplified. However, the invention is not limited thereto. The invention can also be applied to any vibration device for vibrating a predetermined vibration region of a vibration film. For example, when vibrating a desired vibration region of a vibration plate (vibration film) used in a microphone, a speaker, or the like, a desired vibration region may be formed by supporting a surface on one side in the thickness direction of the vibration film with a partition wall of an opening of a substrate and bonding the other surface to a sealing plate through a suppressing portion.

As the ultrasonic measurement apparatus **1**, a configuration for measuring the internal tomographic structure of the living body has been exemplified. However, the ultrasonic measurement apparatus **1** can also be used as a measurement apparatus for examining the internal structure of concrete, such as a concrete building, for example.

In addition, although the ultrasonic measurement apparatus **1** including the ultrasonic sensor **22** has been exemplified. However, the invention can also be applied to other ultrasonic apparatuses. For example, the invention can also be used for an ultrasonic washing machine including an ultrasonic transducer that washes an object to be cleaned by sending ultrasonic waves to the object to be cleaned.

In addition, specific structures when implementing the invention may be formed by appropriately combining the embodiments and the modification examples described above in a range where the object of the invention can be achieved, or may be appropriately changed to other structures in a range where the object of the invention can be achieved.

The entire disclosure of Japanese Patent Application No. 2016-020036, filed on Feb. 4, 2016 is expressly incorporated by reference herein.

What is claimed is:

1. An ultrasonic transducer, comprising:

a substrate in which an opening is formed;

a vibration film that is provided on the substrate so as to close the opening;

a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film;

a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and

a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to, and sandwiched between, both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.

2. The ultrasonic transducer according to claim 1, wherein a connection wiring line connected to the vibration element is provided on the vibration film, and the suppressing portion contains a conductive filler, and is connected to the connection wiring line.

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3. The ultrasonic transducer according to claim 2, wherein the support substrate has a wiring portion, which is connected to the suppressing portion, on a surface facing the vibration film.
4. The ultrasonic transducer according to claim 3, wherein the support substrate includes a penetrating electrode that penetrates the support substrate in a thickness direction to connect the wiring portion and a circuit board, on which a circuit for controlling the vibration element is provided, to each other.
5. An ultrasonic probe, comprising:
an ultrasonic transducer; and
a housing in which the ultrasonic transducer is housed, wherein the ultrasonic transducer includes:
a substrate in which an opening is formed;
a vibration film that is provided on the substrate so as to close the opening;
a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film;
a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and
a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to, and sandwiched between, both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.
6. An ultrasonic apparatus, comprising:
an ultrasonic transducer; and
a control unit that controls the ultrasonic transducer, wherein the ultrasonic transducer includes:
a substrate in which an opening is formed;
a vibration film that is provided on the substrate so as to close the opening;
a plurality of vibration elements that perform at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film and that are disposed at positions where the vibration film and the opening overlap each other in a plan view along a thickness direction of the vibration film;
a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and

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- a suppressing portion that is provided between the adjacent vibration elements in the plan view, is bonded to, and sandwiched between, both the vibration film and the support substrate, and is formed of a resin material for suppressing transmission of vibration of the vibration film.
7. An ultrasonic transducer manufacturing method, comprising:
forming, on a vibration film of a substrate in which the vibration film is provided, a plurality of vibration elements for performing at least one of driving processing for driving the vibration film to vibrate and detection processing for detecting vibration of the vibration film;
forming a suppressing portion, which is formed of a resin material for suppressing transmission of vibration of the vibration film, on a surface of the vibration film not facing the substrate and between the adjacent vibration elements in a plan view along a thickness direction of the vibration film;
making a support substrate, which has a surface facing the vibration film as a flat surface, face the surface of the vibration film not facing the substrate and bonding the other end portion of the suppressing portion, which is on an opposite side to one end portion of the suppressing portion connected to the vibration film, to the support substrate by heating; and
forming an opening in the substrate such that the plurality of vibration elements are disposed at positions where the vibration film and the opening overlap each other in the plan view,
wherein the suppressing portion is bonded to, and sandwiched between, both the vibration film and the support substrate.
8. A vibration device, comprising:
a vibration film that has a predetermined thickness and is able to vibrate in a thickness direction;
a support substrate that is disposed so as to face the vibration film, supports the vibration film, and has a surface facing the vibration film as a flat surface; and
a suppressing portion that is provided along a vibration region in the vibration film and suppresses transmission of vibration of the vibration region of the vibration film to a region other than the vibration region,
wherein the suppressing portion is formed of a resin material, and is bonded to, and sandwiched between, both the vibration film and the support substrate.

* * * * *

专利名称(译)	超声波换能器，超声波探头，超声波装置，超声波换能器制造方法和振动装置		
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摘要(译)

一种超声波传感器，包括：基板，其中形成有开口；振动膜，设置在基板上以封闭开口；多个振动元件设置在沿振动膜的厚度方向的平面图中振动膜和开口彼此重叠的位置处；密封板，其设置成面对振动膜，支撑振动膜，并且具有面向振动膜的表面作为平坦表面；并且，在平面图中设置在相邻的振动元件之间的抑制部分与振动膜和密封板结合，并且由用于抑制振动膜的振动传递的树脂材料形成。

